

# bq769x0 3 节串联至 15 节串联电池监控系列

## 用于锂离子和磷酸盐电池应用

**ECCN: EAR99**

## 1 介绍

### 1.1 特性

- 模拟前端 (AFE) 监控特性
  - 纯数字接口
  - 内部模数转换器 (ADC) 测量电池电压、芯片温度和外部热敏电阻
  - 一个单独的、内部 ADC 测量电池组电流 (库伦电荷计数器)
  - 直接支持多达三个热敏电阻 (103AT)
- 硬件保护特性
  - 放电过流 (OCD)
  - 放电短路 (SCD)
  - 过压 (OV)
  - 欠压 (UV)
- 次级保护器故障检测
- 其他特性
  - 集成电池均衡场效应晶体管 (FET)
  - 充电、放电低侧 NCH FET 驱动器
  - 到主机微控制器的警报中断
  - 2.5V 或 3.3V 输出电压稳压器
  - 无需 EEPROM 编程
  - 高电源电压最大绝对值 (高达 108V)
  - 简单 I<sup>2</sup>C™ 兼容接口 (循环冗余校验 (CRC) 选项)
  - 随机电池连接耐受

### 1.2 应用范围

- 轻型机动车辆 (LEV): 电动自行车 (eBike), 电动踏板车 (eScooter), 脚踏电动自行车 (Pedelec) 和踏板辅助自行车
- 电动和园艺工具
- 后备电池和不间断电源 (UPS) 系统
- 无线基站后备系统
- 12V, 18V, 24V, 36V 和 48V 电池组

### 1.3 说明

bq769x0 系列稳健耐用模拟前端 (AFE) 器件作为针对下一代高功率系统 (诸如轻型机动车辆、电动工具和不间断电源) 的完整电池组监控和保护解决方案的一部分。bq769x0 在设计时充分考虑低功率要求: 可启用/禁用集成电路 (IC) 中的子块来控制整个芯片功耗, 以及可将电池组置于超低功率状态的 SHIP 模式。

bq76920 器件支持多达 5 节串联电池或者典型值为 18V 的电池组; bq76930 处理多达 10 节串联电池或典型值为 36V 的电池组; 而 bq76940 可以与多达 15 节串联电池或者典型值为 48V 的电池组一同工作。可使用这些 AFE 对多种电池化学成分进行管理, 其中包括锂离子、磷酸铁锂, 以及更多的化学成分。

通过 I<sup>2</sup>C, 主机控制器可以使用 bq769x0 来执行很多电池组管理功能, 诸如监视 (电池电压、电池组电流、电池组温度), 保护 (控制充电/放电 FET), 以及均衡功能。集成模数 (A/D) 转换器可实现对关键系统参数的纯数字读取, 这些参数的校准在 TI 制造过程中处理。

#### 器件信息<sup>(1)</sup>

产品型号	封装	封装尺寸 (标称值)
bq76920	薄型小外形尺寸封装 (TSSOP) (20)	6.50mm x 4.40mm
bq76930	TSSOP (30)	7.80mm x 4.40mm
bq76940	TSSOP (44)	11.00mm x 4.40mm

(1) 要了解所有可用封装, 请见数据表末尾的可订购产品附录。



UNLESS OTHERWISE NOTED this document contains PRODUCTION DATA information current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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**2 修订历史记录**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

<b>Changes from Revision B (April 2014) to Revision C</b>		<b>Page</b>
•	Changed 某些文档格式 .....	<u>1</u>
•	Changed some devices from Product Preview to Production Data .....	<u>3</u>
•	Changed content in the I <sup>2</sup> C Communications section .....	<u>26</u>
•	Changed a bit name in PROTECT1 register .....	<u>33</u>
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<b>Changes from Revision A (December 2013) to Revision B</b>		<b>Page</b>
•	Changed Ordering Information table to Device Comparison table .....	<u>3</u>
•	Changed some devices to Product Preview .....	<u>3</u>
•	Changed R <sub>f</sub> max value .....	<u>11</u>
•	Changed verbiage in I <sup>2</sup> C Communications .....	<u>26</u>
•	Changed SYS_STAT D6 bit name .....	<u>29</u>

<b>Changes from Original (October 2013) to Revision A</b>		<b>Page</b>
•	Changed 数据手册的标题 .....	<u>1</u>
•	Changed some devices from Product Preview to Production Data .....	<u>3</u>
•	Changed the t <sub>INDCELL</sub> test condition .....	<u>13</u>
•	Deleted duplicate CELLBAL3 table .....	<u>31</u>
•	Changed bq76940 with bq783xx Companion Controller IC Schematic .....	<u>43</u>

### 3 说明（继续）

为了进一步增加电池组的可靠性，bq769x0 包括针对电压 (OV, UV) 和电流 (OCD, SCD) 的硬件保护功能。德州仪器 (TI) 将它们预先设定为特定的阈值和延迟，这些值可由主机微控制器在电池组启动时更新。

在功率 FET 控制方面，bq769x0 提供两个低侧 FET 驱动器，充电 (CHG) 和放电 (DSG)。这些驱动器可被用来直接操作低侧功率 NCH FET，或者用信号通知外部电路启用高侧 PCH 或 NCH FET。一个专用 ALERT 输入/输出引脚作为主机微控制器的中断信号，快速将 AFE 内的状态更新通知给微控制器。这也许包括一个故障事件或可被读取的库伦电荷计数器采样。可由一个次级保护器从外部驱动 ALERT 引脚，以提供一个禁用 CHG 和 DSG 信号的冗余方式，并可实现更高的系统可视性。

### 4 Device Comparison Table

TUBE	TAPE & REEL	CELLS	I <sup>2</sup> C ADDRESS (7-Bit)	LDO (V)	CRC	PACKAGE
bq7692000PW	bq7692000PWR	3–5	0x08	2.5	No	20-TSSOP (PW)
bq7692001PW <sup>(1)</sup>	bq7692001PWR <sup>(1)</sup>				Yes	
bq7692002PW <sup>(1)</sup>	bq7692002PWR <sup>(1)</sup>			3.3	No	
bq7692003PW	bq7692003PWR				Yes	
bq7692006PW	bq7692006PWR				No	
bq7693000DBT	bq7693000DBTR	6–10	0x08	2.5	No	30-TSSOP (DBT)
bq7693001DBT <sup>(1)</sup>	bq7693001DBTR <sup>(1)</sup>				Yes	
bq7693002DBT <sup>(1)</sup>	bq7693002DBTR <sup>(1)</sup>			3.3	No	
bq7693003DBT	bq7693003DBTR				Yes	
bq7693006DBT	bq7693006DBTR				No	
bq7694000DBT	bq7694000DBTR	9–15	0x08	2.5	No	44-TSSOP (DBT)
bq7694001DBT	bq7694001DBTR				Yes	
bq7694002DBT	bq7694002DBTR			3.3	No	
bq7694003DBT	bq7694003DBTR				Yes	
bq7694006DBT	bq7694006DBTR				No	

(1) Product Preview only

Texas Instruments pre-configures the bq769x0 devices for a specific I<sup>2</sup>C address, LDO voltage, and more. These settings are permanently stored in EEPROM and cannot be further modified.

Contact Texas Instruments for other options not listed above, as well as any options noted as “Product Preview only.”

## 5 Pin Configuration and Functions

### 5.1 Versions

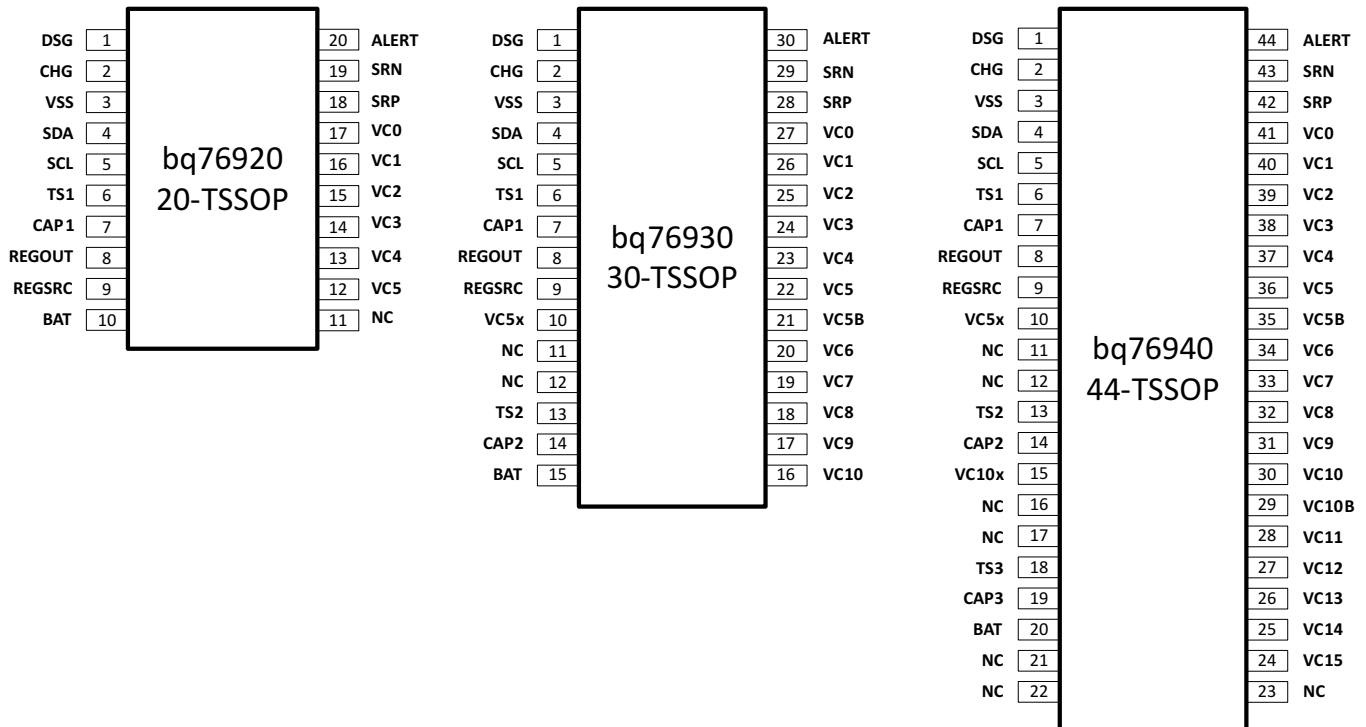


Figure 5-1. Pin Versions

bq76920: 3-5 Series Cells (20-TSSOP)

- 6.5 mm x 4.4 mm x 1.2 mm

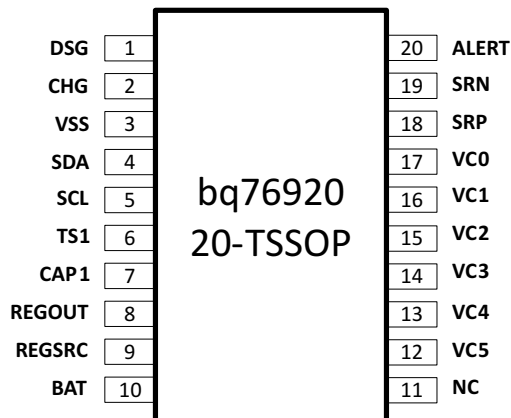
bq76930: 6-10 Series Cells (30-TSSOP)

- 7.8 mm x 4.4 mm x 1.2 mm

bq76940: 9-15 Series Cells (44-TSSOP)

- 11.3 mm x 4.4 mm x 1.2 mm

## 5.2 bq76920 Pin Diagram

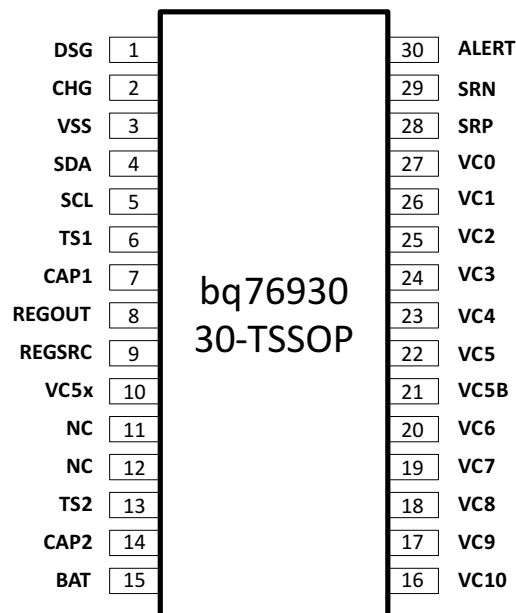


### 5.2.1 bq76920 Pin Map

**bq76920 Pin Functions**

PIN	NAME	TYPE	DESCRIPTION
1	DSG	O	Discharge FET driver
2	CHG	O	Charge FET driver
3	VSS	—	Chip VSS
4	SDA	I/O	I <sup>2</sup> C communication to the host controller
5	SCL	I/O	I <sup>2</sup> C communication to the host controller
6	TS1	I	Thermistor #1 positive terminal
7	CAP1	O	Capacitor to VSS
8	REGOUT	P	Output LDO
9	REGSRC	I	Input source for output LDO
10	BAT	P	Battery (top-most) terminal
11	NC	—	No connect
12	VC5	I	Sense voltage for 5th cell positive terminal
13	VC4	I	Sense voltage for 4th cell positive terminal
14	VC3	I	Sense voltage for 3rd cell positive terminal
15	VC2	I	Sense voltage for 2nd cell positive terminal
16	VC1	I	Sense voltage for 1st cell positive terminal
17	VC0	I	Sense voltage for 1st cell negative terminal
18	SRP	I	Negative current sense (nearest VSS)
19	SRN	I	Positive current sense
20	ALERT	I/O	Alert output and override input

### 5.3 bq76930 Pin Diagram



#### 5.3.1 bq76930 Pin Map

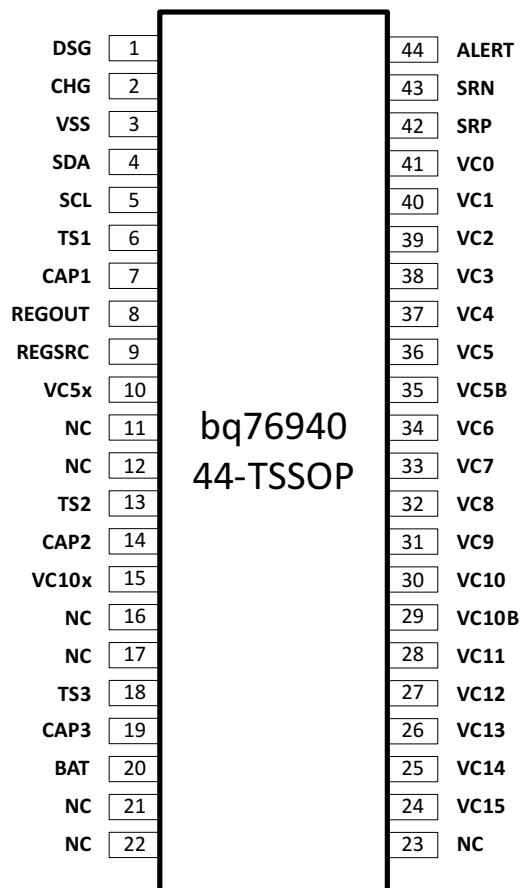
**bq76930 Pin Functions**

PIN	NAME	TYPE	DESCRIPTION
1	DSG	O	Discharge FET driver
2	CHG	O	Charge FET driver
3	VSS	—	Chip VSS
4	SDA	I/O	I <sup>2</sup> C communication to the host controller
5	SCL	I/O	I <sup>2</sup> C communication to the host controller
6	TS1	I	Thermistor #1 positive terminal
7	CAP1	O	Capacitor to VSS
8	REGOUT	P	Output LDO
9	REGSRC	I	Input source for output LDO
10	VC5X	I	Thermistor #2 negative terminal
11	NC	—	No connect (short to CAP2)
12	NC	—	No connect (short to CAP2)
13	TS2	I	Thermistor #2 positive terminal
14	CAP2	O	Capacitor to VC5X
15	BAT	P	Battery (top-most) terminal
16	VC10	I	Sense voltage for 10th cell positive terminal
17	VC9	I	Sense voltage for 9th cell positive terminal
18	VC8	I	Sense voltage for 8th cell positive terminal
19	VC7	I	Sense voltage for 7th cell positive terminal
20	VC6	I	Sense voltage for 6th cell positive terminal
21	VC5B	I	Sense voltage for 6th cell negative terminal
22	VC5	I	Sense voltage for 5th cell positive terminal
23	VC4	I	Sense voltage for 4th cell positive terminal
24	VC3	I	Sense voltage for 3rd cell positive terminal

**bq76930 Pin Functions (continued)**

PIN	NAME	TYPE	DESCRIPTION
25	VC2	I	Sense voltage for 2nd cell positive terminal
26	VC1	I	Sense voltage for 1st cell positive terminal
27	VC0	I	Sense voltage for 1st cell negative terminal
28	SRP	I	Negative current sense (nearest VSS)
29	SRN	I	Positive current sense
30	ALERT	I/O	Alert output and override input

## 5.4 bq76940 Pin Diagram



### 5.4.1 bq76940 Pin Map

**bq76940 Pin Functions**

PIN	NAME	TYPE	DESCRIPTION
1	DSG	O	Discharge FET driver
2	CHG	O	Charge FET driver
3	VSS	—	Chip VSS
4	SDA	I/O	I <sup>2</sup> C communication to the host controller
5	SCL	I/O	I <sup>2</sup> C communication to the host controller
6	TS1	I	Thermistor #1 positive terminal
7	CAP1	O	Capacitor to VSS
8	REGOUT	P	Output LDO
9	REGSRC	I	Input source for output LDO
10	VC5X	I	Thermistor #2 negative terminal
11	NC	—	No connect (short to CAP2)
12	NC	—	No connect (short to CAP2)
13	TS2	I	Thermistor #2 positive terminal
14	CAP2	O	Capacitor to VC5X
15	VC10X	I	Thermistor #3 negative terminal
16	NC	—	No connect (short to CAP3)
17	NC	—	No connect (short to CAP3)



**bq76940 Pin Functions (continued)**

PIN	NAME	TYPE	DESCRIPTION
18	TS3	I	Thermistor #3 positive terminal
19	CAP3	O	Capacitor to VC10X
20	BAT	P	Battery (top-most) terminal
21	NC	—	No connect
22	NC	—	No connect
23	NC	—	No connect
24	VC15	I	Sense voltage for 15th cell positive terminal
25	VC14	I	Sense voltage for 14th cell positive terminal
26	VC13	I	Sense voltage for 13th cell positive terminal
27	VC12	I	Sense voltage for 12th cell positive terminal
28	VC11	I	Sense voltage for 11th cell positive terminal
29	VC10B	I	Sense voltage for 10th cell negative terminal
30	VC10	I	Sense voltage for 10th cell positive terminal
31	VC9	I	Sense voltage for 9th cell positive terminal
32	VC8	I	Sense voltage for 8th cell positive terminal
33	VC7	I	Sense voltage for 7th cell positive terminal
34	VC6	I	Sense voltage for 6th cell positive terminal
35	VC5B	I	Sense voltage for 6th cell negative terminal
36	VC5	I	Sense voltage for 5th cell positive terminal
37	VC4	I	Sense voltage for 4th cell positive terminal
38	VC3	I	Sense voltage for 3rd cell positive terminal
39	VC2	I	Sense voltage for 2nd cell positive terminal
40	VC1	I	Sense voltage for 1st cell positive terminal
41	VC0	I	Sense voltage for 1st cell negative terminal
42	SRP	I	Negative current sense (nearest VSS)
43	SRN	I	Positive current sense
44	ALERT	I/O	Alert output and override input

## 6 Electrical Specifications

### 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT			
$V_{BAT}$	Supply voltage range	(BAT–VSS)	–0.3	36	V			
		(BAT–VC5x), (VC5x–VSS)				bq76930		
		(BAT–VC10x), (VC10x–VC5x), (VC5x–VSS)				bq76940		
$V_I$	Input voltage range	(VCn–VSS) where n = 1..5	–0.3	(n × 7.2)	V			
		(VCn–VSS) where n = 1..5, (VCn–VC5x) where n = 6..10				bq76930		
		(VCn–VSS) where n = 1..5, (VCn–VC5x) where n = 6..10, (VCn–VC10x) where n = 11..15				bq76940		
		Cell input pins, differential (VCn–VCn–1) where n = 1..15/10/5 (bq76940/bq76930/bq76920, respectively)				–0.3	9	V
		SRN, SRP, SCL, SDA				–0.3	3.6	V
		(VC0–VSS), (CAP1–VSS), (TS1–VSS)						
(VC0–VSS), (VC5b–VC5x), (CAP2–VC5x), (CAP1–VSS), (TS2–VC5x), (TS1–VSS)	bq76930							
	(VC0–VSS), (VC5b–VC5x), (VC10b–VC10x), (CAP3–VC10x), (CAP2–VC5x), (CAP1–VSS), (TS3–VC10x), (TS2–VC5x), (TS1–VSS)	bq76940						
	REGSRC	–0.3	36					
$V_O$	Output voltage range	REGOUT, ALERT	–0.3	3.6	V			
		DSG	–0.3	20				
		CHG	–0.3	$V_{CHGCLAMP}$				
$I_{CB}$	Cell balancing current (per cell)	bq76920	70	mA				
		bq76930, bq76940	5	mA				
$I_{DSG}$	Discharge pin input current when disabled (measured into terminal)		7	mA				

### 6.2 Handling Ratings

			MIN	MAX	UNIT
$T_{STG}$	Storage temperature range		–65	150	°C
	Lead temperature (soldering, 10 s)			300	
$V_{ESD}^{(1)}$ Rating	Human body model (HBM) ESD stress voltage <sup>(2)</sup>		–2	2	kV
	Charged device model (CDM) ESD stress voltage <sup>(3)</sup>		–500	500	V

- (1) Electrostatic discharge (ESD) to measure device sensitivity and immunity to damage caused by assembly line electrostatic discharges into the device.
- (2) Level listed above is the passing level per ANSI/ESDA/JEDEC JS-001. JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (3) Level listed above is the passing level per EIA-JEDEC JESD22-C101. JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

### 6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted). See [Section 8.1.1](#) for more information on cell configurations. All voltages are relative to VSS, except "Cell input differential."

PARAMETER		MIN	TYP	MAX	UNIT		
V <sub>BAT</sub>	Supply voltage range	(BAT–VSS)	bq76920		V		
		(BAT–VC5x), (VC5x–VSS)	bq76930				
		(BAT–VC10x), (VC10x–VC5x), (VC5x–VSS)	bq76940				
V <sub>IN</sub>	Input voltage range	Cell input pins, differential (VCn–VCn–1) where n = 1..15/10/5 (bq76940/bq76930/bq76920, respectively), in-use cells only		2	5	V	
		(VCn–VSS) where n = 1..5	bq76920		0	5 x n	V
		(VCn–VSS) where n = 1..5, (VCn–VC5x) where n = 6..10	bq76930				
		(VCn–VSS) where n = 1..5, (VCn–VC5x) where n = 6..10, (VCn–VC10x) where n = 11..15	bq76940				
		SRP			–10	10	mV
		(VC0–VSS)	bq76920				
		(VC0–VSS), (VC5b–VC5x)	bq76930				
		(VC0–VSS), (VC5b–VC5x), (VC10b–VC10x)	bq76940		–200	200	mV
		SRN					
		SCL, SDA					
		(TS1–VSS)	bq76920		0	3.6	V
		(TS1–VSS), (TS2–VC5x)	bq76930				
		(TS1–VSS), (TS2–VC5x), (TS3–VC10x)	bq76940				
REGSRC			6	25			
V <sub>OUT</sub>	Output voltage range	CHG, DSG		0	16	V	
		REGOUT, ALERT				V	
		(CAP1–VSS)	bq76920				
		(CAP1–VSS), (CAP2–VC5x)	bq76930				
(CAP1–VSS), (CAP2–VC5x), (CAP3–VC10x)	bq76940						
I <sub>CB</sub>	Cell balancing current (internal, per cell)	bq76920		0	50	mA	
		bq76930, bq76940		0	5	mA	
R <sub>C</sub>	External cell input resistance	bq76920		40	100	1K	Ω
		bq76930, bq76940		500	1K	1K	Ω
C <sub>C</sub>	External cell input capacitance	0.1	1	10	μF		
R <sub>f</sub>	External supply filter resistance	40	100	1K	Ω		
C <sub>f</sub>	External supply filter capacitance	1	10	40	μF		
R <sub>FILT</sub>	Sense resistor filter resistance	100	1K		Ω		
R <sub>ALERT</sub>	ALERT pin to VSS resistor		1M		Ω		
C <sub>L</sub>	REGOUT loading capacitance	1	4.7		μF		
C <sub>CAP</sub>	REGSRC, CAP1, CAP2 and CAP3 output capacitance	1			μF		
R <sub>TS</sub>	External thermistor nominal resistance (103AT) at 25°C	10K			Ω		
T <sub>OPR</sub>	Operating free-air temperature	–40		85	°C		

## 6.4 Thermal Information

over operating free-air temperature range (unless otherwise noted)

THERMAL METRIC <sup>(1)</sup>	TSSOP			UNIT
	bq76920xy 20 PINS (PW)	bq76930xy 30 PINS (DBT)	bq76940xy 44 PINS (DBT)	
$R_{\theta_{JA, High K}}$ Junction-to-ambient thermal resistance <sup>(2)</sup>	93.7	86.5	70.1	°C/W
$R_{\theta_{JC(top)}}$ Junction-to-case(top) thermal resistance <sup>(3)</sup>	28.7	19.4	17.5	
$R_{\theta_{JB}}$ Junction-to-board thermal resistance <sup>(4)</sup>	44.6	41.3	33.9	
$\Psi_{JT}$ Junction-to-top characterization parameter <sup>(5)</sup>	1.3	0.5	0.5	
$\Psi_{JB}$ Junction-to-board characterization parameter <sup>(6)</sup>	44.1	40.6	33.4	
$R_{\theta_{JC(bottom)}}$ Junction-to-case(bottom) thermal resistance <sup>(7)</sup>	n/a	n/a	n/a	

- (1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, [SPRA953](#).
- (2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
- (3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
- (4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
- (5) The junction-to-top characterization parameter,  $\Psi_{JT}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).
- (6) The junction-to-board characterization parameter,  $\Psi_{JB}$ , estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining  $\theta_{JA}$ , using a procedure described in JESD51-2a (sections 6 and 7).
- (7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

## 6.5 Electrical Characteristics

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with  $V_{CELL} = 4$  V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

PARAMETER	DESCRIPTION	TEST CONDITION	MIN	TYP	MAX	UNIT
<b>SUPPLY CURRENTS</b>						
$I_{DD}$	NORMAL mode: ADC off, CC off	Sum of ICC_BAT and ICC_REGSRC currents		40	60	$\mu$ A
	NORMAL mode: ADC on, CC off			60	90	
	NORMAL mode: ADC off, CC on			110	165	
	NORMAL mode: ADC on, CC on			130	195	
$I_{CC\_BAT}$	NORMAL mode: ADC off	Into BAT pin		30	45	
	NORMAL mode: ADC on			50	75	
$I_{CC\_REGSRC}$	NORMAL mode: CC off	Into REGSRC pin		10	15	
	NORMAL mode: CC on			80	120	
$I_{SHIP}$	SHIP/SHUTDOWN mode	Device in full shutdown, only VSTUP/BG and BOOT detector on		0.6	1.8	

**Electrical Characteristics (continued)**

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with  $V_{CELL} = 4$  V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

PARAMETER	DESCRIPTION	TEST CONDITION	MIN	TYP	MAX	UNIT
<b>LEAKAGE AND OFFSET CURRENTS</b>						
$dI_{NOM}$	NORMAL mode supply current offset	Measured into VC5x (bq76930, bq76940) and VC10x (bq76940)	–5	±2.5	5	μA
$dI_{SHIP}$	SHIP mode supply current offset		–1.0	±0.1	1.0	
$dI_{ALERT}$	Supply current when ALERT active	Measured into VC5x (bq76930, bq76940) or added to BAT (bq76920)		15	25	
$dI_{CELL}$	Cell measurement input current	Measured into VC0–VC15 except VC5, VC10, VC15	–0.3	±0.1	0.3	
		Measured into VC5, VC10, VC15			0.5	
$I_{LKG}$	Terminal input leakage				1	
<b>INTERNAL POWER CONTROL (STARTUP and SHUTDOWN)</b>						
$V_{PORA}$	Analog POR threshold	See Note	4		5	V
$V_{SHUT}$	Shutdown voltage	See Note			3.6	V
$t_{I2CSTARTUP}$	Time delay after boot signal on TS1 before I <sup>2</sup> C communications allowed	Delay after boot sequence when I <sup>2</sup> C communication is allowed		1		ms
$t_{BOOTREADY}$	Device boot startup delay	Delay after boot signal when device has completed full boot-up sequence			10	ms
$T_{SHUTD}$	Thermal shutdown voltage			100	150	°C
<b>MEASUREMENT SCHEDULE</b>						
$t_{VCELL}$	Cell voltage measurement interval	bq76920, bq76930, bq76940		250		ms
$t_{INDCELL}$	Individual cell measurement time	Per cell, balancing off		50		
		Per cell, balancing on		12.5		
$t_{CB\_RELAX}$	Cell balancing relaxation time before cell voltage measured			12.5		
$t_{TEMP\_DEC}$	Temperature measurement decimation time	Measurement duration for temperature reading		12.5		
$t_{BAT}$	Pack voltage calculation interval			250		
$t_{TEMP}$	Temperature measurement interval	Period of measurement of either TS1/TS2/TS3 or internal die temp		2		s
<b>14-BIT ADC FOR CELL VOLTAGE AND TEMPERATURE MEASUREMENT</b>						
$ADC_{RANGE}$	ADC measurement recommend operation range	$V_{CELL}$ measurements	2		5	V
		TS/Temp measurements	0.3		3	V
$ADC_{LSB}$	ADC LSB value			382		μV
$ADC_{25A}$	ADC cell voltage accuracy	$V_{CELL} = 3.6 - 4.3$ V	–40	±10	40	mV
$ADC_{25B}$		$V_{CELL} = 3.2 - 4.6$ V	–40	±15	40	
$ADC_{25C}$		$V_{CELL} = 2.0 - 5.0$ V	–50	±25	50	
$ADC_{60}$	ADC cell voltage accuracy temperature drift adder from 25°C	$T_A = 0^{\circ}\text{C}$ to $60^{\circ}\text{C}$	–10		10	
$ADC_{TS}$	ADC thermistor measurement accuracy	Input from 0.3 to 3.0 V, BAT > 7 V	–35		35	
<b>16-BIT CC FOR PACK CURRENT MEASUREMENT</b>						
$CC_{RANGE}$	CC input voltage range		–200		200	mV
$CC_{FSR}$	CC full scale range		–270		270	mV

## Electrical Characteristics (continued)

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with  $V_{CELL} = 4$  V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

PARAMETER	DESCRIPTION	TEST CONDITION	MIN	TYP	MAX	UNIT
CC <sub>LSB</sub>	CC LSB value	CC running constantly		8.44		μV
tCC <sub>READ</sub>	Conversion time	Single conversion		250		ms
CC <sub>INL</sub>	Integral nonlinearity	16-bit, best fit over input voltage range ± 200 mV		± 2	± 40	LSB
CC <sub>OFFSET</sub>	Offset error			± 1	± 3	LSB
CC <sub>GAIN</sub>	Gain error	Over input voltage range		± 0.5%	± 1.5%	FSR
CC <sub>GAINDRIFT</sub>	Gain error drift	Over input voltage range			150	PPM / °C
CC <sub>RIN</sub>	Effective input resistance			2.5		MΩ
<b>THERMISTOR BIAS</b>						
R <sub>TS</sub>	Pull-up resistance	TA = 25°C	9.85	10	10.15	kΩ
R <sub>TS</sub> DRIFT	Pull-up resistance across temp	TA = –40°C to 85°C	9.7		10.3	kΩ
<b>DIETEMP</b>						
V <sub>DIETEMP25</sub>	Die temperature voltage	TA = 25°C		1.20		V
V <sub>DIETEMPDRIFT</sub>	Die temperature voltage drift			–4.2		mV/°C
<b>INTEGRATED HARDWARE PROTECTIONS</b>						
OV <sub>RANGE</sub>	OV threshold range		0x2008		0x2FF8	ADC
UV <sub>RANGE</sub>	UV threshold range		0x1000		0x1FF0	ADC
OV <sub>UVSTEP</sub>	OV and UV threshold step size			16		LSB
UV <sub>MINQUAL</sub>	UV minimum value to qualify	Below UV <sub>MINQUAL</sub> , cell is shorted (unused)		0x0518		ADC
OV <sub>DELAY</sub>	OV delay timer options	OV delay = 1 s	0.7	1	1.75	s
		OV delay = 2 s	1.6	2	2.75	
		OV delay = 4 s	3.5	4	5	
		OV delay = 8 s	7	8	10	
UV <sub>DELAY</sub>	UV delay timer options	UV delay = 1 s	0.7	1	1.75	
		UV delay = 4 s	3.5	4	5	
		UV delay = 8 s	7	8	10	
		UV delay = 16 s	14	16	20	
OCD <sub>RANGE</sub>	OCD threshold options	Measured across (SRP–SRN)	8		100	mV
OCD <sub>STEP</sub>	OCD threshold step size	RSNS = 0		2.78		mV
		RSNS = 1		5.56		mV
OCD <sub>DELAY</sub>	OCD delay options		10		1280	ms
SCD <sub>RANGE</sub>	SCD threshold options	Measured across (SRP–SRN)	22		200	mV
SCD <sub>STEP</sub>	SCD threshold step size	RSNS = 0		11.1		mV
		RSNS = 1		22.2		mV
SCD <sub>DELAY</sub>	SCD delay options		35	70	105	μs
			50	100	150	μs
			140	200	260	μs
			280	400	520	μs
t <sub>PROTACC</sub>	Delay accuracy for OCD		–20%		20%	
OC <sub>OFFSET</sub>	OCD and SCD voltage offset		–2.5		2.5	mV
OC <sub>SCALEERR</sub>	OCD and SCD scale accuracy		–10%		10%	

## Electrical Characteristics (continued)

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with  $V_{CELL} = 4$  V. Min and max values include full recommended operating condition temperature range from –40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

PARAMETER	DESCRIPTION	TEST CONDITION	MIN	TYP	MAX	UNIT
<b>CHARGE AND DISCHARGE DRIVERS</b>						
$V_{FETON}$	CHG and DSG on	REGSRC $\geq$ 12 V with load resistance of 10 M $\Omega$	10	12	14	V
		REGSRC < 12 V with load resistance of 10 M $\Omega$	REGSRC –2	REGSRC –1	REGSRC	V
$t_{FET\_ON}$	CHG and DSG ON rise time	CHG/DSG driving an equivalent load capacitance of 10 nF, measured from 10% to 90% of $V_{FETON}$		200	250	$\mu$ s
$t_{DSG\_OFF}$	DSG pull-down OFF fall time	DSG driving an equivalent load capacitance of 10 nF, measured from 90% to 10%		60	90	$\mu$ s
$R_{CHG\_OFF}$	CHG pull-down OFF resistance to VSS	When CHG disabled, CHG held at 12 V	750	1000	1250	k $\Omega$
$R_{DSG\_OFF}$	DSG pull-down OFF resistance to VSS	When DSG disabled, DSG held at 12 V	1.75	2.50	4.25	k $\Omega$
$V_{LOAD\_DETECT}$	Load detection threshold		0.4	0.7	1.0	V
$V_{CHG\_CLAMP}$	CHG clamp voltage	If the CHG pin externally pulled high (through PACK–, if load applied), 500 $\mu$ A max sink current into CHG pin. With CHG_ON bit cleared.	18	20	22	V
<b>ALERT PIN</b>						
$V_{ALERT\_OH}$	ALERT output voltage high	$I_{OL} = 1$ mA	REGOUT x 0.75			V
$V_{ALERT\_OL}$	ALERT output voltage low	Unloaded	REGOUT x 0.25			V
$V_{ALERT\_IH}$	ALERT input high	ALERT externally forced high when internally driven low	1			V
$R_{ALERT\_PD}$	ALERT pin weak pulldown resistance when driven low	Measured into ALERT pin with ALERT = REGOUT	0.8	2.5	8	M $\Omega$
<b>CELL BALANCING DRIVER</b>						
$R_{DSFET}$	Internal cell balancing driver resistance	$V_{CELL} = 3.6$ V	1	5	10	$\Omega$
$X_{BAL}$	Cell balancing duty cycle when enabled	Every 250 ms		70%		
<b>EXTERNAL REGULATOR</b>						
$V_{EXTLDO}$	External LDO voltage options	Nominal values, TI factory programmed, unloaded, across temp	2.45	2.50	2.55	V
			3.20	3.30	3.40	V
$V_{EXTLDO\_LN}$	Line regulation	REGSRC pin stepped from 6 to 25 V, with 10 mA load, in 100 $\mu$ s			100	mV
$V_{EXTLDO\_LD}$	Load regulation	IREGOUT = 0 mA to 10 mA	–4%		4%	
$V_{EXTLDO\_DC}$	External LDO minimum voltage under DC load	REGOUT = 10 mA DC, 2.5-V version	2.4			V
		REGOUT = 20 mA DC, 2.5-V version	2.3			V
		REGOUT = 10 mA DC, 3.3-V version	3.15			V
		REGOUT = 20 mA DC, 3.3-V version	3.05			V
$I_{EXTLDO\_LIMIT}$	External LDO current limit	REGOUT = 0 V	30	38	45	mA
<b>BOOT DETECTOR</b>						
$V_{BOOT}$	Boot threshold voltage	Measured at TS1 pin with device in SHIP mode. Below MIN, device will not boot up. Above MAX, device will be guaranteed to boot up.	300		1000	mV

## Electrical Characteristics (continued)

Typical conditions are measured at 25°C with nominal BAT voltages of 18 V (bq76920), 36 V (bq76930), or 48 V (bq76940) with  $V_{CELL} = 4$  V. Min and max values include full recommended operating condition temperature range from -40°C to +85°C. Certain characteristics may be shown at different voltage or temperature ranges, as clarified in the Test Condition sections.

PARAMETER	DESCRIPTION	TEST CONDITION	MIN	TYP	MAX	UNIT
$t_{BOOT\_max}$	Boot threshold application time	Measured at TS1 pin. Below MIN, device will not boot up. Above MAX, device will be guaranteed to boot up.	10		2000	$\mu$ s
<b>I<sup>2</sup>C COMPATIBLE INTERFACE</b>						
$V_{IL}$	Input Low Logic Threshold				REGOUT x 0.25	V
$V_{IH}$	Input High Logic Threshold		REGOUT x 0.75			V
$V_{OL}$	Output Low Logic Drive	$I_{OL} = 1$ mA			0.20	V
$t_f$	SCL, SDA Fall Time	$I_{OL} = 2.5$ mA			0.40	
$V_{OH}$	Output High Logic Drive (Not applicable due to open-drain outputs)		N/A		N/A	V
$t_{HIGH}$	SCL Pulse Width High		4.0			$\mu$ s
$t_{LOW}$	SCL Pulse Width Low		4.7			$\mu$ s
$t_{SU;STA}$	Setup time for START condition		4.7			$\mu$ s
$t_{HD;STA}$	START condition hold time after which first clock pulse is generated		4.0			$\mu$ s
$t_{SU;DAT}$	Data setup time		250			ns
$t_{HD;DAT}$	Data hold time		0			$\mu$ s
$t_{SU;STO}$	Setup time for STOP condition		4.0			$\mu$ s
$t_{BUF}$	Time the bus must be free before new transmission can start		4.7			$\mu$ s
$t_{VD;DAT}$	Clock Low to Data Out Valid				900	ns
$t_{HD;DAT}$	Data Out Hold Time After Clock Low		0			ns
$f_{SCL}$	Clock Frequency		0		100	kHz

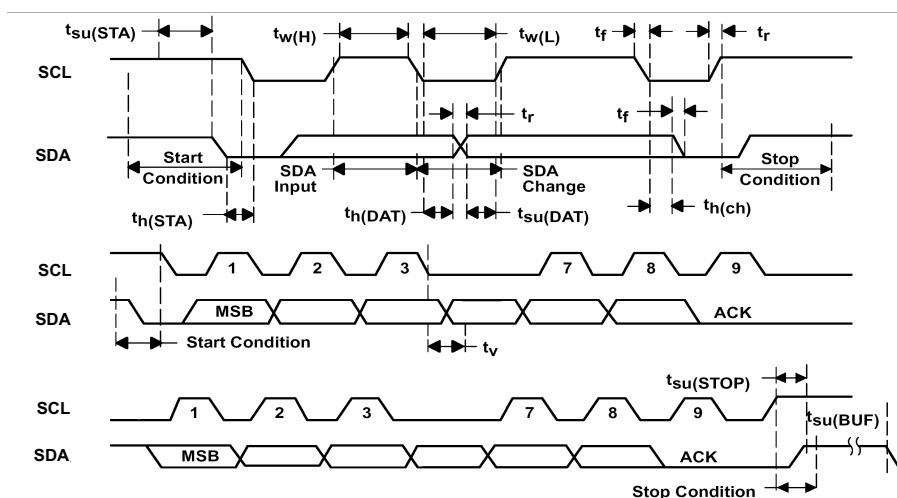


Figure 6-1. I<sup>2</sup>C Timing



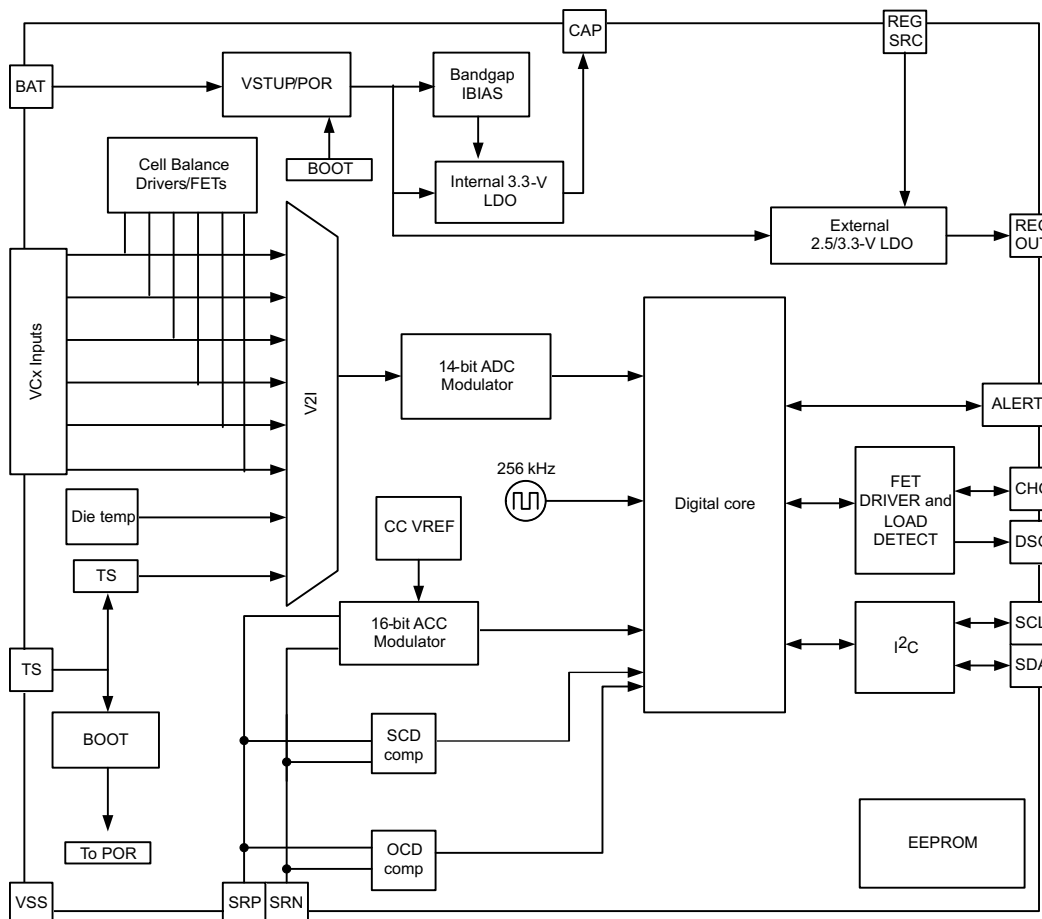
## 7 Detailed Description

### 7.1 Overview

In the bq769x0 family of analog front-end (AFE) devices, the bq76920 device supports up to 5-series cells, the bq76930 device supports up to 10-series cells, and the bq76940 device supports up to 15-series cells. Via I<sup>2</sup>C, a host controller can use the bq769x0 to implement battery pack management functions, such as monitoring (cell voltages, pack current, pack temperatures), protection (controlling charge/discharge FETs), and balancing. Integrated A/D converters enable a purely digital readout of critical system parameters including cell voltages and internal or external temperature, with calibration handled in TI's manufacturing process. For an additional degree of pack reliability, the bq769x0 includes hardware protections for voltage (OV, UV) and current (OCD, SCD).

The bq769x0 provides two low-side FET drivers, charge (CHG) and discharge (DSG), which may be used to directly manipulate low-side power NCH FETs, or as signals that control an external circuit that enables high-side PCH or NCH FETs. A dedicated ALERT input/output pin serves as an interrupt signal to the host microcontroller, quickly informing the microcontroller of an updated status in the AFE. This may include a fault event or that a coulomb counter sample is available for reading. An available ALERT pin may also be driven externally by a secondary protector to provide a redundant means of disabling the CHG and DSG signals and higher system visibility.

### 7.2 Functional Block Diagram



## 7.3 Feature Description

### 7.3.1 Subsystems

bq769x0 consists of three major subsystems: Measurement, Protection, and Control. These work in harmony to ensure that the fundamental battery pack parameters—voltage, current and temperature—are accurately captured and easily available to a host controller, while ensuring a baseline or secondary level of hardware protection in the event that a host controller is unable or unavailable to manage certain fault conditions.

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#### NOTE

The bq769x0 is intended to serve as an analog front-end (AFE) as part of a chipset system solution: A companion microcontroller is required to oversee and control this AFE.

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The Measurement subsystem's core responsibility is to digitize the cell voltages, pack current (integrated into a passed charge calculation), external thermistor temperature, and internal die temperature. It also performs an automatic calculation of the total battery stack voltage, by simply adding up all measured cell voltages.

The Protection subsystem provides a baseline or secondary level of hardware protections to better support a battery pack's FMEA requirements in the event of a loss of host control or simply if a host is unable to respond to a certain fault event in time. Integrated protections include pack-level faults such as OV, UV, OCD, SCD; detection of an external secondary protector fault; and internal "watchdog"-style device fault. Protection events will trigger toggling of the ALERT pin, as well as automatic disabling of the DSG and/or CHG FET driver (depending on the fault). Recovery from a fault event must be handled by the host microcontroller.

The Control subsystem implements a suite of useful pack features, including direct low-side NCH FET drivers, cell balancing drivers, the ALERT digital output, an external LDO and more.

The following sections describe each subsystem in greater detail, as well as explaining the various power states that are available.

#### 7.3.1.1 Measurement Subsystem Overview

The monitoring subsystem ensures that all cell voltages, temperatures, and pack current may be easily measured by the host. All ADCs are trimmed by TI.

ADC and CC data are always returned as atomic values if both high and low registers are read in the same transaction (using address auto-increment).

##### 7.3.1.1.1 Data Transfer to the Host Controller

The bq769x0 has a fully digital interface: All information is transferred through I<sup>2</sup>C, simply by reading and/or writing to the appropriate register(s) storing the relevant data. Block reads and writes, buffered by an 8-bit CRC code per byte, ensure a fast and robust transmission of data.

##### 7.3.1.1.2 14-Bit ADC

Each bq769x0 device measures cell voltages and temperatures using a 14-bit ADC. This ADC measures all differential cell voltages, thermistors and/or die temperature with a nominal full-scale unsigned range of 0–6.275 V and LSB of 382  $\mu$ V.

To enable the ADC, the *[ADC\_EN]* bit in the SYS\_CTRL1 register must be set. This bit is set automatically whenever the device enters NORMAL mode. When enabled, the ADC ensures that the integrated OV and UV protections are functional.

For each contiguous set of five cells (VC1 to VC5, VC6 to VC10), when no cells in that particular set are being balanced, each cell is measured over a 50-ms decimation window and a complete update is available every 250 ms. In the bq76930 and bq76940, every set of five cells above the primary five cells is measured in parallel. The 50-ms decimation greatly assists with removing the aliasing effects present in a noisy motor environment.

When any cells in a contiguous set of 5 cells are being balanced, those affected cells are measured in a reduced 12.5-ms decimation period, to allow the cell balancing to function properly without affecting the integrated OV and UV protections. Since cell balancing is typically only performed during pack charge or idle periods, the shortened decimation periods should not impact accuracy as the system noise during these times is greatly reduced. This reduced decimation period is only applied to sets where one of the cells is being balanced.

This is summarized as follows for the bq76920–bq76940:

- VC1 to VC5 measurements are each taken in a 50-ms decimation period when all bits in CELLBAL1 register are 0, and a 12.5-ms decimation period when any bits in CELLBAL1 register are 1.
- VC6 to VC10 measurements are each taken in a 50-ms decimation period when all bits in CELLBAL2 register are 0, and a 12.5-ms decimation period when any bits in CELLBAL2 register are 1.
- VC11 to VC15 measurements are each taken in a 50-ms decimation period when all bits in CELLBAL3 register are 0, and a 12.5-ms decimation period when any bits in CELLBAL3 register are 1.
- Total update interval is 250 ms.

Each differential cell input is factory-trimmed for gain and/or offset, such that the resulting reading via I<sup>2</sup>C is always consistent from part-to-part and requires no additional calibration or correction factor application.

The ADC is required to be enabled in order for the integrated OV and UV protections to be operating.

The following shows how to convert the 14-bit ADC reading into an analog voltage. Each device is factory calibrated, with a GAIN and OFFSET stored into EEPROM.

The ADC transfer function is a linear equation defined as follows:

$$V(\text{cell}) = \text{GAIN} \times \text{ADC}(\text{cell}) + \text{OFFSET} \quad (1)$$

GAIN is stored in units of  $\mu\text{V}/\text{LSB}$ , while OFFSET is stored in mV units.

Some example cell voltage calculations are provided in the table below. For illustration purposes, the example uses a hypothetical GAIN of 380  $\mu\text{V}/\text{LSB}$  (ADCGAIN<4:0> = 0x0F) and OFFSET of 30 mV (ADCOFFSET<7:0> = 0x1E).

14-Bit ADC Result	ADC Result in Decimal	GAIN ( $\mu\text{V}/\text{LSB}$ )	OFFSET (mV)	Cell Voltage (mV)
0x1800	6144	380	30	2365
0x1F10	7952	380	30	3052

#### NOTE

When entering NORMAL mode from SHIP mode, please allow for the following times before reading out initial cell voltage data:

bq76920: 250 ms

bq76930: 400 ms

bq76940: 800 ms

#### 7.3.1.1.2.1 Optional Real-time Calibration Using the Host Microcontroller

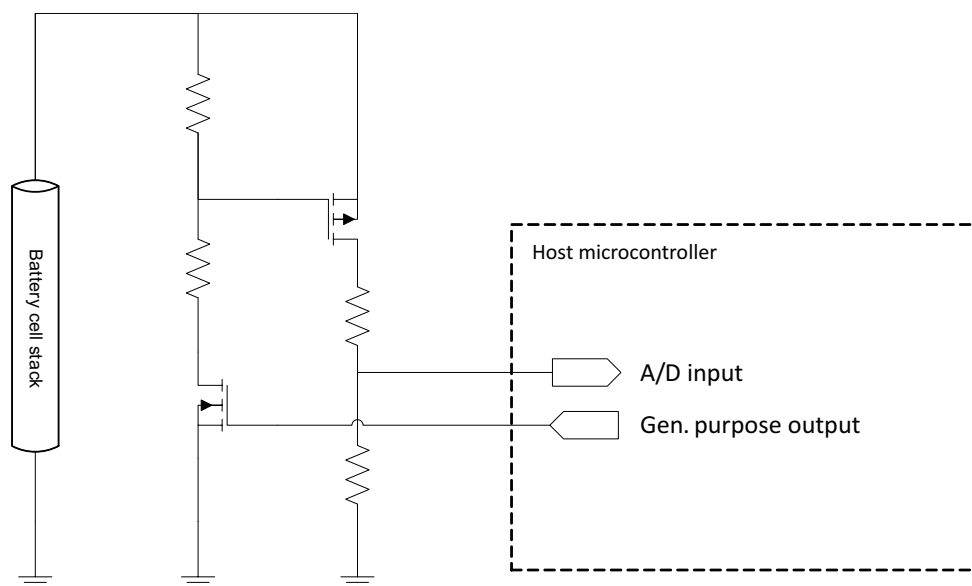
The performance of the cell voltage values measured by the 14-bit ADC has a factory-calibrated accuracy, as follows:

- +/- 10 mV TYP, +/- 40 mV MIN and MAX from 3.6 to 4.3 V,

- +/- 15 mV TYP, +/- 40 mV MIN and MAX from 3.2 to 4.6 V, and
- +/- 50 mV MIN and MAX from 2.0 to 5.0 V

While this is suitable for the majority of pack protection and basic monitoring applications the bq769x0 AFE family is intended to support, certain systems may require a higher accuracy performance.

To achieve this, use an available ADC channel and general purpose output terminal on the host microcontroller paired with the bq769x0. A simple external circuit consisting of two precision resistors and a small-signal FET is activated by the host microcontroller to determine the total stack voltage,  $V_{STACK}$ ; this is then compared against the sum of the individual cell voltages as measured by the internal ADC of the bq769x0. The resulting transfer function coefficient,  $GAIN_2$ , is simply applied to each cell voltage ADC value for improved accuracy.



**Figure 7-1. External Real-Time Calibration Circuit to Host Microcontroller**

The process is as follows:

1. Periodically measure  $V_{STACK}$ .
  - (a)  $V_{STACK} = V_{AD} \times (R1 + R2) / R1$
2. Read out all  $V_{CELL}$  ADC readings from the bq769x0 and apply the standard GAIN and OFFSET values stored in the bq769x0.
  - (a)  $V(1) = GAIN \times ADC_1 + OFFSET$ ,  $V(2) = GAIN \times ADC_2 + OFFSET$ , and so on
3. Sum up all  $V_{CELL}$  values,  $V_{SUM}$ .
  - (a)  $V_{SUM} = V(1) + V(2) + V(3) \dots$
4. Calculate  $GAIN_2$ .
  - (a)  $GAIN_2 = V_{STACK} / V_{SUM}$

As a general recommendation, a new  $GAIN_2$  function should be generated when the cell voltages increase or decrease by more than 100 mV. With  $GAIN_2$ , each cell voltage calculation becomes:

$$V(\text{cell}) = GAIN_2 \times (GAIN \times ADC(\text{cell}) + OFFSET) \quad (2)$$

For systems that do not require this additional in-use calibration function,  $GAIN_2$  is simply "1".

### 7.3.1.1.3 16-Bit CC

A 16-bit integrating ADC, commonly referred to as the coulomb counter (CC), provides measurements of accumulated charge across the current sense resistor. The integration period for this reading is 250 ms.

The CC may be operated in one of two modes: ALWAYS ON and 1-SHOT.

- In ALWAYS ON mode, the CC runs at 100%, gathering a fresh reading every 250 ms. The conclusion of each reading sets the CC\_READY bit, which toggles the ALERT pin high to inform the microcontroller that a new reading is available. To enable Always On mode, set [CC\_EN] = 1.
- In 1-SHOT mode, the CC performs a single 250-ms reading, and similarly sets the CC\_READY bit when completed. This mode is intended for non-gauging usages, where the host simply desires to check the pack current.

To enable a 1-SHOT reading, ensure [CC\_EN] = 0 and set [CC\_ONESHOT] = 1.

The full scale range of the CC is  $\pm 270$  mV, with a max recommended input range of  $\pm 200$  mV, thus yielding an LSB of approximately 8.44  $\mu$ V.

The following equation shows how to convert the 16-bit CC reading into an analog voltage if no board-level calibration is performed:

$$\text{CC Reading (in } \mu\text{V)} = [\text{16-bit 2's Complement Value}] \times (8.44 \mu\text{V/LSB}) \quad (3)$$

16-Bit CC Result	ADC Result in Decimal	CC Reading (in $\mu$ V)
0x0001	1	8.44
0x2710	10000	84,400
0x7D00	32000	270,080
0x8300	-32000	-270,080
0xC350	-15536	-131,123.84
0xFFFF	-1	-8.44

#### 7.3.1.1.4 External Thermistor

One (bq76920), two (bq76930), or three (bq76940) 10 k $\Omega$  NTC 103AT thermistors may be measured by the device. These are measured by applying a factory-trimmed internal 10k pull-up resistance to an internal regulator value of nominally 3.3 V, the result of which can be read out from the TSx (TS1, TS2, TS3) registers.

To select thermistor measurement mode, set [TEMP\_SEL] = 1.

Thermistor TS1 is connected between TS1 and VSS; TS2 is connected between TS2 and VC5x (bq76930 and bq76940 only); and TS3 is connected between TS3 and VC10x (bq76940 only). These thermistors may be placed in various areas in the battery pack to measure such things as localized cell temperature, FET heating, etc.

The thermistor impedance may be calculated using the 14-bit ADC reading in the TS1/TS2/TS3 registers and 10k internal pull-up resistance as follows:

The following equations show how to use the 14-bit ADC readings in TS1, TS2, and TS3 to determine the resistance of the external 103AT thermistor:

$$V_{TSX} = (\text{ADC in Decimal}) \times 382 \mu\text{V/LSB} \quad (4)$$

$$R_{TS} = (10,000 \times V_{TSX}) \div (3.3 - V_{TSX}) \quad (5)$$

To convert the thermistor resistance into temperature, please refer to the thermistor component manufacturer's datasheet.

#### 7.3.1.1.5 Die Temperature Monitor

##### NOTE

When switching between external and internal temperature monitoring, a 2-s latency may be incurred due to the natural scheduler update interval.

A die temperature block generates a voltage that is proportional to the die temperature, and provides a way of reducing component count if pack thermistors are not used or ensuring that the die power dissipation requirements are observed. The die is measured using the same on-board 14-bit ADC as the cell voltages.

To select internal die temperature measurement mode, set  $[TEMP\_SEL] = 0$ .

For bq76930 and bq76940, multiple die temperature measurements are available; these are stored in TS2 and TS3.

To convert a DIETEMP reading into temperature, refer to the following equation box. If more accurate temperature readings are needed from DIETEMP, the DIETEMP at room temperature value should be stored during production calibration.

The following equation shows how to use the 14-bit ADC readings in TS1, TS2, and TS3 when  $[TEMPSEL] = 0$  to determine the internal die temperature:

$$V_{25} = 1.200 \text{ V (nominal)} \quad (6)$$

$$V_{TSX} = (\text{ADC in Decimal}) \times 382 \mu\text{V/LSB} \quad (7)$$

$$TEMP_{DIE} = 25^\circ - ((V_{TSX} - V_{25}) \div 0.0042) \quad (8)$$

### 7.3.1.1.6 16-Bit Pack Voltage

Once converted to digital form, each cell voltage is added up and the summation result stored in the BAT registers. This 16-bit value has a nominal LSB of 1.532 mV.

The following shows how to convert the 16-bit pack voltage ADC reading into an analog voltage. This value also uses the GAIN and OFFSET stored into EEPROM.

The ADC transfer function is a linear equation defined as follows:

$$V_{(BAT)} = 4 \times \text{GAIN} \times \text{ADC}(\text{cell}) + (\#\text{Cells} \times \text{OFFSET}) \quad (9)$$

GAIN is stored in units of  $\mu\text{V/LSB}$ , while OFFSET is stored in mV units.

### 7.3.1.1.7 System Scheduler

A master scheduler oversees the monitoring intervals, creating a full update every 250 ms. Temperature measurements are taken every 2 seconds. Pack voltage is calculated every 250 ms.

## 7.3.1.2 Protection Subsystem

### 7.3.1.2.1 Integrated Hardware Protections

Integrated hardware protections are provided as an extra degree of safety and are meant to supplement the standard protection feature set that would be incorporated into the host controller firmware. They should not be used as the sole means of protecting a battery pack, but are useful for FMEA purposes; for example, in the event that a host microcontroller is unable to react to any of the below protection situations. All hardware protection thresholds and delays should be loaded into the AFE by the host microcontroller during system startup. The AFE will also default to pre-defined threshold and delay settings, in case the host microcontroller is unable to or does not wish to program the protection settings.

Overcurrent in Discharge (OCD) and Short Circuit in Discharge (SCD) are implemented using sampled analog comparators that run at 32 kHz, and that continuously monitor the voltage across (SRP–SRN) while the device is in NORMAL mode. Upon detection of a voltage that exceeds the programmed OCD or SCD threshold, a counter begins to count up to a programmed delay setting. If the counter reaches its target value, the SYS\_STAT register is updated to indicate the fault condition, the FET state(s) are updated as shown in Table 3, and the ALERT pin is driven high to interrupt the host.

The protection fault threshold and delay settings for OCD and SCD protections are configured via the PROTECT1 and PROTECT2 registers. See the Register Map section for details about supported values.

Overvoltage (OV) and Undervoltage (UV) protections are handled digitally, by comparing the cell voltage readings against the 8-bit programmed thresholds in the OV and UV registers.

The OV threshold is stored in the OV\_TRIP register and is a direct mapping of 8 bits of the 14-bit ADC reading, with the upper 2 MSB preset to “10” and lower 4 LSB preset to “1000”. In other words, the corresponding OV trip level is mapped to “10-XXXX-XXXX-1000”. The programmable range of OV thresholds is approximately 3.15 to 4.7 V, but this is subject to variation of to the (GAIN, OFFSET) linear equation used to map the ADC values.

The UV threshold is stored in the UV\_TRIP register and is a direct mapping of 8 bits of the 14-bit ADC reading, with the upper 2 MSB preset to “01” and lower 4 LSB preset to “0000”. In other words, the corresponding OV trip level is mapped to “01-XXXX-XXXX-0000”. The programmable range of UV thresholds is approximately 1.58 to 3.1 V, but this is subject to variation due to the (GAIN, OFFSET) linear equation used to map the ADC values.

Protection	Upper 2 MSB	Middle 8 Bits	Lower 4 LSB
OV	10	Set in OV_TRIP Register	1000
UV	01	Set in UV_TRIP Register	0000

#### NOTE

To support flexible cell configurations within bq76920, bq76930, and bq76940, UV is ignored on any cells that have a reading under  $UV_{MINQUAL}$ . This allows cell pins to be shorted in implementations where not all cells are needed (for example, 6-series cells using the bq76930).

Default protection thresholds and delays are shown in the register description at the end of this datasheet. These are loaded into the digital register (RAM) of the device when the device enters NORMAL mode. These RAM values may then be overwritten by the host controller to any other values, which they will retain until a POR event. It is recommended that the host controller reload these values during its standard power-up and/or re-initialization sequence.

To calculate the correct OV\_TRIP and UV\_TRIP register values for a device, use the following procedure:

1. Determine desired OV.
2. Read out  $[ADCGAIN]$  and  $[ADCOFFSET]$  from their corresponding registers. Note that ADCGAIN is stored in units of  $\mu\text{V}/\text{LSB}$ , while ADCOFFSET is stored in mV.
3. Calculate the full 14-bit ADC value needed to meet the desired OV and UV trip thresholds as follows:
  - (a)  $OV\_TRIP\_FULL = (OV - ADCOFFSET) \div ADCGAIN$
  - (b)  $UV\_TRIP\_FULL = (UV - ADCOFFSET) \div ADCGAIN$
4. Remove the upper 2 MSB and lower 4 LSB from the full 14-bit value, retaining only the remaining middle 8 bits. This can be done by shifting the OV\_TRIP\_FULL and UV\_TRIP\_FULL binary values 4 bits to the right and removing the upper 2 MSB.
5. Write OV\_TRIP and UV\_TRIP to their corresponding registers.

Both OV and UV protections require the ADC to be enabled. Ensure that the  $[ADC\_EN]$  bit is set to 1 if OV and UV protections are needed.

#### 7.3.1.2.2 Reduced Test Time

A special debug and test configuration bit is provided in the SYS\_CTRL2 register, called  $[DELAY\_DIS]$ . Setting  $[DELAY\_DIS]$  bypasses the OV/UV protection fault timers and allows a fault condition to be registered within 200 ms after application of such a fault condition.

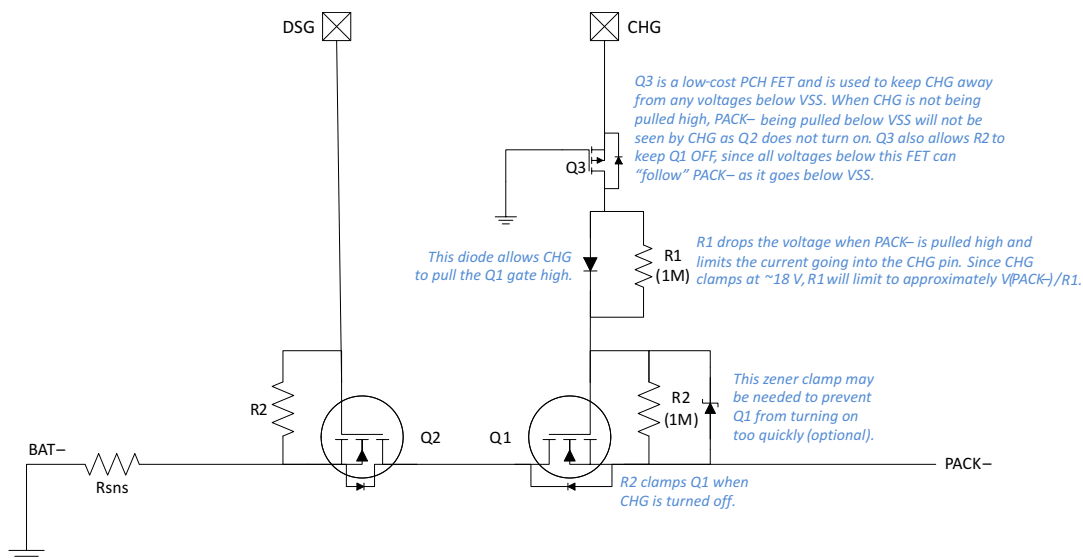
### 7.3.1.3 Control Subsystem

#### 7.3.1.3.1 FET Driving (CHG AND DSG)

Each bq769x0 device provides two low-side FET drivers, CHG and DSG, which control NCH power FETs or may be used as a signal to enable various other circuits such as a high-side NCH charge pump circuit.

Both DSG and CHG drivers have a fast pull-up to nominally 12 V when enabled. DSG uses a fast pull-down to VSS when disabled, while CHG utilizes a high impedance (nominally 1 M $\Omega$ ) pull-down path when disabled.

An additional internal clamp circuit ensures that the CHG pin does not exceed a maximum of 20 V.



**Figure 7-2. CHG AND DSG FET Circuit**

The power path for the CHG and DSG pull-up circuit originates from the REGSRC pin, instead of BAT.

To enable the CHG fet, set the [CHG\_ON] register bit to 1; to disable, set [CHG\_ON] = 0. The discharge FET may be similarly controlled via the [DSG\_ON] register bit.

Certain fault conditions or power state transitions will clear the state of the CHG/DSG FET controls. [Table 7-1](#) shows what action, if any, are taken to [CHG\_ON] and [DSG\_ON] in response to various system events:

**Table 7-1. CHG, DSG Response Under Various System Events**

EVENT	[CHG_ON]	[DSG_ON]
OV Fault	Set to 0	—
UV Fault	—	Set to 0
OCD Fault	—	Set to 0
SCD Fault	—	Set to 0
ALERT Override	Set to 0	Set to 0
DEVICE_XREADY gets set	Set to 0	Set to 0
Enter SHIP mode from NORMAL	Set to 0	Set to 0



#### NOTE

All protection recovery must be initiated by the host microcontroller. In order to resume FET operation after a fault condition has occurred, the host microcontroller must first clear the corresponding status bit in the SYS\_STAT register, which will clear the ALERT pin, and then manually re-enable the CHG and/or DSG bit. Certain faults, such as OV or UV, may immediately re-toggle if such a condition still persists. Refer to [Table 7-3](#) for details on clearing status bits.

There are no conditions under which the bq769x0 automatically sets either *[CHG\_ON]* or *[DSG\_ON]* to 1.

#### 7.3.1.3.2 Load Detection

A load detection circuit is present on the CHG pin and activated whenever the CHG FET is disabled (*[CHG\_ON]* = 0). This circuit detects if the CHG pin is externally pulled high when the high impedance (approximately 1 MΩ) pull-down path should actually be holding the CHG pin to VSS, and is useful for determining if the PACK– pin (outside of the AFE) is being held at a high voltage—for example, if the load is present while the power FETs are off. The state of the load detection circuit is read from the *[LOAD\_PRESENT]* bit of the SYS\_CTRL1 register.

After an OCD or SCD fault has occurred, the DSG FET will be disabled (*[DSG\_ON]* cleared), and the CHG FET must similarly be explicitly disabled to activate the load detection circuit. The host microcontroller may periodically poll the *[LOAD\_PRESENT]* bit to determine the state of the PACK– pin and determine when the load is removed (*[LOAD\_PRESENT]* = 0).

#### 7.3.1.3.3 Cell Balancing

Both internal and external passive cell balancing options are fully supported by the bq76920, while external cell balancing is recommended for bq76930 and bq76940. It is left to the host controller to determine the exact balancing algorithm to be used in any given system; each bq769x0 device provides the cell voltages and balancing drivers to enable this. If using the internal cell balance drivers, up to 50 mA may be balanced per cell. If using external cell balancing, much higher balancing currents may be employed.

To activate a particular cell balancing channel, simply set the corresponding bit for that cell in the CELLBAL1, CELLBAL2, or CELLBAL3 register. For example, VC1–VC0 is enabled by setting *[CB1]*, while VC12–VC11 is set via *[CB12]*.

Multiple cells may be simultaneously balanced; it is left to the user's discretion to determine the ideal number of cells to concurrently balance. Adjacent cells should not be balanced simultaneously; this may cause cell pins to exceed their absolute maximum conditions and is also not recommended for external balancing implementations. Additionally, if internal balancing is used, care should be taken to avoid exceeding package power dissipation ratings.

#### NOTE

The host controller must ensure that no two adjacent cells are balanced simultaneously within each set of the following:

- VC1–VC5
- VC6–VC10
- VC11–VC15

The total duty cycle devoted to balancing is approximately 70% per 250 ms. This is because a portion of the 250 ms is allotted for normal cell voltage measurements via the ADC.

If  $[ADC\_EN] = 1$ , OV and UV protections are not affected by cell balancing, since the cell balancing is temporarily suspended for a small slice of time every 250 ms during which the cell voltage readings are taken. This ensures that the OV and UV protections do not accidentally trigger, or miss an actual OV/UV condition on the cells while balancing is enabled.

#### NOTE

All cell balancing control bits in CELLBAL1, CELLBAL2, and CELLBAL3 are automatically cleared under the following events, and must be explicitly re-written by the host microcontroller following clearing of the event:

- DEVICE\_XREADY gets set
- Enters NORMAL mode from SHIP mode

#### 7.3.1.3.4 Alert

The ALERT pin serves as an active high digital interrupt signal that can be connected to a GPIO port of the host microcontroller. This signal is an OR of all bits in the SYS\_STAT register.

In order to clear the ALERT signal, the source bit in the SYS\_STAT register must first be cleared by writing a “1” to that bit. This will cause an automatic clear of the ALERT pin once all bits are cleared.

The ALERT pin may also be driven by an external source; for example, the pack may include a secondary overvoltage protector IC. When the ALERT pin is forced high externally while low, the device will recognize this as an OVRD\_ALERT fault and set the  $[OVRD\_ALERT]$  bit. This triggers automatic disabling of both CHG and DSG FET drivers. The device cannot recognize the ALERT signal input high when it is already forcing the ALERT signal high from another condition.

An external pull-down resistor of 500 k $\Omega$ –1 M $\Omega$  from ALERT to VSS is highly recommended.

#### 7.3.1.3.5 Output LDO

An adjustable output voltage regulator LDO is provided as a simple way to provide power to additional components in the battery pack, such as the host microcontroller or LEDs. The LDO is configured in EEPROM by TI during the production test process, and can support 2.5-V or 3.3-V options.

A cascode small-signal FET must be added in the external path between BAT and REGSRC. This helps drop most of the power dissipation outside of the package and cuts down on package power dissipation.

#### 7.3.1.4 Communications Subsystem

The AFE implements a standard 100-kHz I<sup>2</sup>C interface and acts as a slave device. The I<sup>2</sup>C device address is 7-bits and is factory programmed; consult the Device Comparison Table (Section 4) of this datasheet for more information.

A write transaction is shown in Figure 7-3. Block writes are allowed by sending additional data bytes before the Stop. The I<sup>2</sup>C block will auto-increment the register address after each data byte.

When enabled, the CRC is calculated over the register address and data. Block writes are achieved by sending additional data and CRC byte pairs, where each subsequent CRC is calculated only over the byte being sent. The CRC polynomial is  $x^8 + x^2 + x + 1$ , and the initial value is 0.

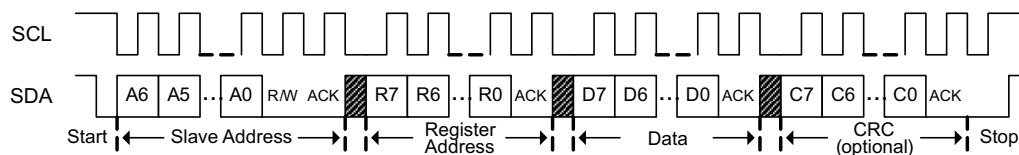


Figure 7-3. I<sup>2</sup>C Write

Figure 7-4 shows a read transaction using a Repeated Start.

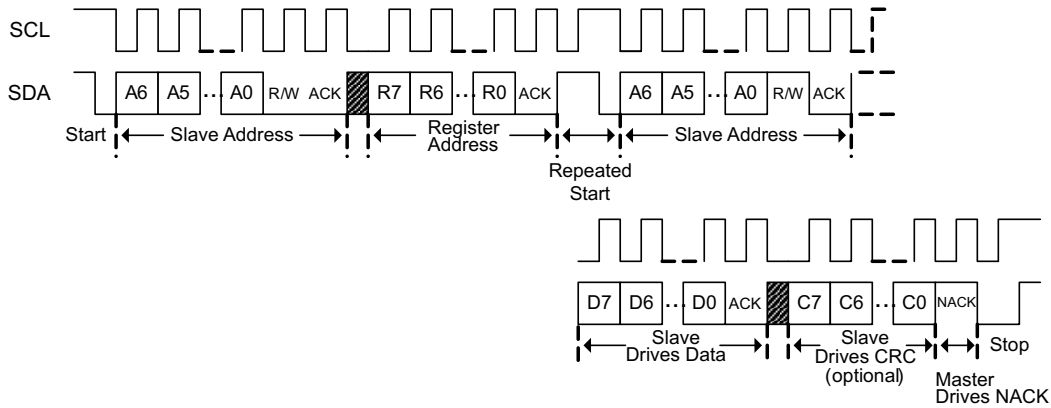


Figure 7-4. I<sup>2</sup>C Read with Repeated Start

Figure 7-5 shows a read transaction where a Repeated Start is not used, for example if not available in hardware. For a block read the master ACK's each data byte except the last and continues to clock the interface. The I<sup>2</sup>C block will auto-increment the register address after each data byte. When enabled, the CRC is calculated only over the second slave address and data. Similar to a block write, in a block read with CRC enabled each additional read byte is followed by a CRC byte calculated over only that byte.

When detecting a bad CRC, the I<sup>2</sup>C Slave will NACK the CRC and go to an idle state.

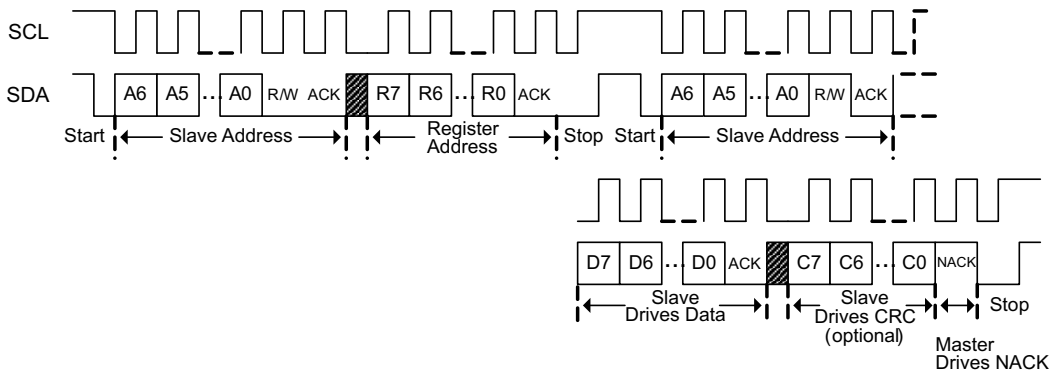


Figure 7-5. I<sup>2</sup>C Read Without Repeated Start

## 7.4 Device Functional Modes

Each bq769x0 device supports the following modes of operation.

Table 7-2. Supported Power Modes

Mode	Description
NORMAL	Fully operational state. Both ADC and CC may be on, or disabled by host microcontroller. OV and UV protection enabled if ADC is on. OCD and SCD enabled. ADC and CC may be disabled to reduce power consumption, and CC may be operated in a "1-SHOT" mode for flexible power savings.
SHIP	Lowest possible power state, intended for pack assembly and/or long term pack storage. Must see a BOOT signal (> 1 VBOOT) on TS1 pin to boot from SHIP → NORMAL. Note that the device always enters SHIP mode upon POR.

### 7.4.1 NORMAL Mode

NORMAL mode represents the fully operational mode where all blocks are enabled and the device sees its highest current consumption. In this mode, certain blocks/functions may be disabled to save power—these include the ADC and CC. OV and UV are running continuously as long as the ADC is enabled. The OCD and SCD comparators may not be disabled in this mode.

Transitioning from NORMAL to SHIP mode is also initiated by the host, and requires consecutive writes to two bits in the SYS\_CTRL1 register.

### 7.4.2 SHIP Mode

SHIP mode is the basic and lowest power mode that bq769x0 supports. SHIP mode is automatically entered during initial pack assembly and after every POR event. When the device is in NORMAL mode, it may enter SHIP by the host controller via a specific sequence of I<sup>2</sup>C commands.

In SHIP mode, only a minimum of blocks are turned on, including the VSTUP power supply and primal boot detector. Waking from SHIP mode to NORMAL mode requires pulling the TS1 pin greater than VBOOT, which triggers the device boot-up sequence.

To enter SHIP mode from NORMAL mode, the [SHUTA] and [SHUTB] bits in the SYS\_CTRL1 register must be written with specific patterns across two consecutive writes:

- Write #1: [SHUTA] = 0, [SHUTB] = 1
- Write #2: [SHUTA] = 1, [SHUTB] = 0

Note that [SHUTA] and [SHUTB] should each be in a 0 state prior to executing the shutdown command above. If this specific sequence is entered into the device, the device transitions into SHIP mode. If any other sequence is written to the [SHUTA] and [SHUTB] bits or if either of the two patterns is not correctly entered, the device will not enter SHIP mode.

#### CAUTION

DO NOT OPERATE THE DEVICE BELOW POR. When designing with the bq76940, the intermediate voltages (BAT–VC10x), (VC10x–VC5x) and (VC5x–VSS) must each never fall below VSHUT. When this occurs, a full device reset must be initiated by powering down all three intermediate voltages (BAT–VC10x), (VC10x–VC5x) and (VC5x–VSS) below VSHUT and rebooting by applying the appropriate VBOOT signal to the TS1 pin. When designing with the bq76930, the intermediate voltages (BAT–VC5x) and (VC5x–VSS) must each never fall below VSHUT. When this occurs, a full device reset must be initiated by powering down both intermediate voltages (BAT–VC5x) and (VC5x–VSS) below VSHUT and rebooting by applying the appropriate VBOOT signal to the TS1 pin.

The device will also enter SHIP mode during a POR event; however, this is not a recommended method of SHIP mode entry. If any of the supply-side voltages below fall below V<sub>SHUT</sub> and then back up above VPORA, the device defaults into the SHIP mode state. This is similar to an initial pack assembly condition. In order to exit SHIP mode into NORMAL mode, the device must follow the standard boot sequence by applying a voltage greater than the VBOOT threshold on the TS1 pin.

## 7.5 Register Maps

Name	Addr	D7	D6	D5	D4	D3	D2	D1	D0
READ/WRITE									
SYS_STAT	0x00	CC_READY	RSVD	DEVICE_XREADY	OVRD_ALERT	UV	OV	SCD	OCD
CELLBAL1	0x01						CB<5:1>		
CELLBAL2 <sup>(1)</sup>	0x02						CB<10:6>		
CELLBAL3 <sup>(2)</sup>	0x03						CB<15:11>		
SYS_CTRL1	0x04	LOAD_PRESENT			ADC_EN	TEMP_SEL	RSVD	SHUT_A	SHUT_B
SYS_CTRL2	0x05	DELAY_DIS	CC_EN	CC_ONESHOT	RSVD			DSG_ON	CHG_ON
PROTECT1	0x06	RSNS			SCD_DELAY		SCD_THRESH		
PROTECT2	0x07	OCD_DELAY				OCD_THRESH			
PROTECT3	0x08	UV_DELAY		OV_DELAY		RSVD			
OV_TRIP	0x09	OV_THRESH							
UV_TRIP	0x0A	UV_THRESH							
CC_CFG	0x0B	Must be programmed to 0x19							
READ-ONLY									
VC1_HI	0x0C						<13:8>		
VC1_LO	0x0D				<7:0>				
VC2_HI	0x0E						<13:8>		
VC2_LO	0x0F				<7:0>				
VC3_HI	0x10						<13:8>		
VC3_LO	0x11				<7:0>				
VC4_HI	0x12						<13:8>		
VC4_LO	0x13				<7:0>				
VC5_HI	0x14						<13:8>		
VC5_LO	0x15				<7:0>				
VC6_HI <sup>(1)</sup>	0x16						<13:8>		
VC6_LO <sup>(1)</sup>	0x17				<7:0>				
VC7_HI <sup>(1)</sup>	0x18						<13:8>		
VC7_LO <sup>(1)</sup>	0x19				<7:0>				
VC8_HI <sup>(1)</sup>	0x1A						<13:8>		
VC8_LO <sup>(1)</sup>	0x1B				<7:0>				
VC9_HI <sup>(1)</sup>	0x1C						<13:8>		
VC9_LO <sup>(1)</sup>	0x1D				<7:0>				
VC10_HI <sup>(1)</sup>	0x1E						<13:8>		
VC10_LO <sup>(1)</sup>	0x1F				<7:0>				
VC11_HI <sup>(2)</sup>	0x20						<13:8>		
VC11_LO <sup>(2)</sup>	0x21				<7:0>				
VC12_HI <sup>(2)</sup>	0x22						<13:8>		
VC12_LO <sup>(2)</sup>	0x23				<7:0>				
VC13_HI <sup>(2)</sup>	0x24						<13:8>		
VC13_LO <sup>(2)</sup>	0x25				<7:0>				
VC14_HI <sup>(2)</sup>	0x26						<13:8>		
VC14_LO <sup>(2)</sup>	0x27				<7:0>				
VC15_HI <sup>(2)</sup>	0x28						<13:8>		
VC15_LO <sup>(2)</sup>	0x29				<7:0>				
BAT_HI	0x2A				<15:8>				
BAT_LO	0x2B				<7:0>				
TS1_HI	0x2C						<13:8>		
TS1_LO	0x2D				<7:0>				

(1) These registers are only valid for bq76930 and bq76940.

(2) These registers are only valid for bq76940.

Name	Addr	D7	D6	D5	D4	D3	D2	D1	D0
TS2_HI <sup>(1)</sup>	0x2E								<13:8>
TS2_LO <sup>(1)</sup>	0x2F								<7:0>
TS3_HI <sup>(2)</sup>	0x30								<13:8>
TS3_LO <sup>(2)</sup>	0x31								<7:0>
CC_HI	0x32								<15:8>
CC_LO	0x33								<7:0>
ADCGAIN1	0x50				RSVD			ADCGAIN<4:3>	RSVD
ADCOFFSET	0x51								ADCOFFSET<7:0>
ADCGAIN2	0x59					ADCGAIN<2:0>			RSVD

### 7.5.1 Detailed Information

**Table 7-3. SYS\_STAT (0x00)**

BIT	7	6	5	4	3	2	1	0
NAME	CC_READY	RSVD	DEVICE_XREADY	OVRD_ALERT	UV	OV	SCD	OCD
RESET	0	0	0	0	0	0	0	0
ACCESS	RW	RW	RW	RW	RW	RW	RW	RW

#### NOTE

Bits in SYS\_STAT may be cleared by writing a "1" to the corresponding bit.

Writing a "0" does not change the state of the corresponding bit.

**CC\_READY (Bit 7):** Indicates that a fresh coulomb counter reading is available. Note that if this bit is not cleared between two adjacent CC readings becoming available, the bit remains latched to 1. This bit may only be cleared (and not set) by the host.

0 = Fresh CC reading not yet available or bit is cleared by host microcontroller.

1 = Fresh CC reading is available. Remains latched high until cleared by host.

**RSVD (Bit 6):** Reserved. Do not use.

**DEVICE\_XREADY (Bit 5):** Internal chip fault indicator. When this bit is set to 1, it should be cleared by the host. May be set due to excessive system transients. This bit may only be cleared (and not set) by the host.

0 = Device is OK.

1 = Internal chip fault detected, recommend that host microcontroller clear this bit after waiting a few seconds. Remains latched high until cleared by the host.

**OVRD\_ALERT (Bit 4):** External pull-up on the ALERT pin indicator. Only active when ALERT pin is not already being driven high by the AFE itself.

0 = No external override detected

1 = External override detected. Remains latched high until cleared by the host.

**UV (Bit 3):** Undervoltage fault event indicator.

0 = No UV fault is detected.

1 = UV fault is detected. Remains latched high until cleared by the host.

**OV (Bit 2):** Overvoltage fault event indicator.

0 = No OV fault is detected.

1 = OV fault is detected. Remains latched high until cleared by the host.

**SCD (Bit 1):** Short circuit in discharge fault event indicator.

0 = No SCD fault is detected.

1 = SCD fault is detected. Remains latched high until cleared by the host.

**OCD (Bit 0):** Over current in discharge fault event indicator.

0 = No OCD fault is detected.

1 = OCD fault is detected. Remains latched high until cleared by the host.

**Table 7-4. CELLBAL1 (0x01) for bq76920, bq76930, and bq76940**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	—	CB5	CB4	CB3	CB2	CB1
RESET	0	0	0	0	0	0	0	0
ACCESS	R	R	R	RW	RW	RW	RW	RW

**CBx (Bits 4–0):**

0 = Cell balancing on Cell “x” is disabled.

1 = Cell balancing on Cell “x” is enabled.

**Table 7-5. CELLBAL2 (0x02) for bq76930 and bq76940**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	—	CB10	CB9	CB8	CB7	CB6
RESET	0	0	0	0	0	0	0	0
ACCESS	R	R	R	RW	RW	RW	RW	RW

**CBx (Bits 4–0):**

0 = Cell balancing on Cell “x” is disabled.

1 = Cell balancing on Cell “x” is enabled.

**Table 7-6. CELLBAL3 (0x03) for bq76940**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	—	CB15	CB14	CB13	CB12	CB11
RESET	0	0	0	0	0	0	0	0
ACCESS	R	R	R	RW	RW	RW	RW	RW

**CBx (Bits 4–0):**

0 = Cell balancing on Cell “x” is disabled.

1 = Cell balancing on Cell “x” is enabled.

**Table 7-7. SYS\_CTRL1 (0x04)**

BIT	7	6	5	4	3	2	1	0
NAME	LOAD_PRESENT	—	—	ADC_EN	TEMP_SEL	RSVD	SHUT_A	SHUT_B
RESET	0	0	0	0	0	0	0	0
ACCESS	R	R	R	RW	RW	RW	RW	RW

**LOAD\_PRESENT (Bit 7):** Valid only when [CHG\_ON] = 0. Is high if CHG pin is detected to exceed VLOAD\_DETECT while CHG\_ON = 0, which suggests that external load is present. Note this bit is read-only and automatically clears when load is removed.

- 0 = CHG pin < VLOAD\_DETECT or [CHG\_ON] = 1.
- 1 = CHG pin > VLOAD\_DETECT, while [CHG\_ON] = 0.

**ADC\_EN (Bit 4):** ADC enable command

- 0 = Disable voltage and temperature ADC readings (also disables OV protection)
- 1 = Enable voltage and temperature ADC readings (also enables OV protection)

**TEMP\_SEL (Bit 3):** TSx\_HI and TSx\_LO temperature source

- 0 = Store internal die temperature voltage reading in TSx\_HI and TSx\_LO
- 1 = Store thermistor reading in TSx\_HI and TSx\_LO (all thermistor ports)

**RSVD (Bit 2):** Reserved, do not set to 1.

**SHUT\_A, SHUT\_B (Bits 1–0):** Shutdown command from host microcontroller. Must be written in a specific sequence, shown below.

- 00 then non-01
- then 01 then 10 = Device powers down and enters SHIP mode.
- Other = Device ignores the command.

**Table 7-8. SYS\_CTRL2 (0x05)**

BIT	7	6	5	4	3	2	1	0
NAME	DELAY_DIS	CC_EN	CC_ONESHOT	RSVD	RSVD	RSVD	DSG_ON	CHG_ON
RESET	0	0	0	0	0	0	0	0
ACCESS	RW	RW	RW	RW	RW	RW	RW	RW

**DELAY\_DIS (Bit 7):** Disable OV, UV, OCD, and SCD delays for faster customer production testing.

- 0 = Normal delay settings
- 1 = OV, UV, OCD and SCD delay circuit is bypassed, creating zero delay (approximately 250 ms).

**CC\_EN (Bit 6):** Coulomb counter continuous operation enable command. If set high, [CC\_ONESHOT] bit is ignored.

- 0 = Disable CC continuous readings
- 1 = Enable CC continuous readings and ignore [CC\_ONESHOT] state

**CC\_ONESHOT (Bit 5):** Coulomb counter single 250-ms reading trigger command. If set to 1, the coulomb counter will be activated for a single 250-ms reading, and then turned back off. [CC\_ONESHOT] will also be cleared at the conclusion of this reading, while [CC\_READY] bit will be set to 1.

- 0 = No action
- 1 = Enable single CC reading (only valid if [CC\_EN] = 0), and [CC\_READY] = 0)

**RSVD (Bit 4–2):** Reserved. Do not use.

**DSG\_ON (Bit 1):** Discharge FET driver (low side NCH) or discharge signal control

- 0 = DSG is off.



1 = DSG is on.

**CHG\_ON (Bit 0):** Discharge FET driver (low side NCH) or discharge signal control

0 = CHG is off.

1 = CHG is on.

**Table 7-9. PROTECT1 (0x06)**

BIT	7	6	5	4	3	2	1	0
NAME	RSNS	—	RSVD	SCD_D1	SCD_D0	SCD_T2	SCD_T1	SCD_T0
RESET	TBD	0	0	TBD	TBD	TBD	TBD	TBD
ACCESS	RW	R	RW	RW	RW	RW	RW	RW

**RSNS (Bit 7):** Allows for doubling the OCD and SCD thresholds simultaneously

0 = OCD and SCD thresholds at lower input range

1 = OCD and SCD thresholds at upper input range

**RSVD (Bit 5):** Reserved, do not set to 1.

**SCD\_D1:0 (Bits 4–3):**

Short circuit in discharge delay setting. A 400- $\mu$ s setting is recommended only in systems using maximum cell measurement input resistance,  $R_c$ , of 1 k $\Omega$  (which corresponds to minimum internal cell balancing current or external cell balancing configuration).

Code	(in $\mu$ s)
0x0	70
0x1	100
0x2	200
0x3	400

**SCD\_T2:0 (Bits 2–0):** Short circuit in discharge threshold setting

Code	RSNS = 1 (in mV)	RSNS = 0 (in mV)
0x0	44	22
0x1	67	33
0x2	89	44
0x3	111	56
0x4	133	67
0x5	155	78
0x6	178	89
0x7	200	100

**Table 7-10. PROTECT2 (0x07)**

BIT	7	6	5	4	3	2	1	0
NAME	—	OCD_D2	OCD_D1	OCD_D0	OCD_T3	OCD_T2	OCD_T1	OCD_T0
RESET	0	TBD	TBD	TBD	TBD	TBD	TBD	TBD
ACCESS	R	RW	RW	RW	RW	RW	RW	RW

**OCD\_D2:0 (Bits 6–4):** Overcurrent in discharge delay setting

Code	(in ms)
0x0	10
0x1	20
0x2	40
0x3	80
0x4	160
0x5	320
0x6	640
0x7	1280

**OCD\_T3:0 (Bits 3–0):** Overcurrent in discharge threshold setting.

Code	RSNS = 1 (in mV)	(RSNS = 0 (in mV)
0x0	17	8
0x1	22	11
0x2	28	14
0x3	33	17
0x4	39	19
0x5	44	22
0x6	50	25
0x7	56	28
0x8	61	31
0x9	67	33
0xA	72	36
0xB	78	39
0xC	83	42
0xD	89	44
0xE	94	47
0xF	100	50

**Table 7-11. PROTECT3 (0x08)**

BIT	7	6	5	4	3	2	1	0
NAME	UV_D1	UV_D0	OV_D1	OV_D0	RSVD	RSVD	RSVD	RSVD
RESET	0	0	0	0	1	0	0	0
ACCESS	RW	RW	RW	RW	RW	RW	RW	RW

**UV\_D1:0 (Bits 7–6):** Undervoltage delay setting

Code	(in s)
0x0	1
0x1	4
0x2	8
0x3	16

**OV\_D1:0 (Bits 5–4):** Overvoltage delay setting

Code	(in s)
0x0	1
0x1	2
0x2	4
0x3	8

**RSVD (Bits 3–0):** These bits are for TI internal debug use only and must be configured to the default settings indicated.

**Table 7-12. OV\_TRIP (0x09)**

BIT	7	6	5	4	3	2	1	0
NAME	OV_T7	OV_T6	OV_T5	OV_T4	OV_T3	OV_T2	OV_T1	OV_T0
RESET	1	0	1	0	1	1	0	0
ACCESS	RW	RW	RW	RW	RW	RW	RW	RW

**OV\_T7:0 (Bits 7–0):** Middle 8 bits of the direct ADC mapping of the desired OV protection threshold, with upper 2 MSB set to 10 and lower 2 LSB set to 1000. The equivalent OV threshold is mapped to:  $10\text{-OV\_T}<7:0>1000$ .

By default, OV\_TRIP is configured to a 0xAC setting.

Note that OV\_TRIP is based on the ADC voltage, which requires back-calculation using the GAIN and OFFSET values stored in AD CGAIN<4:0> and ADC OFFSET<7:0>.

**Table 7-13. UV\_TRIP (0x0A)**

BIT	7	6	5	4	3	2	1	0
NAME	UV_T7	UV_T6	UV_T5	UV_T4	UV_T3	UV_T2	UV_T1	UV_T0
RESET	1	0	0	1	0	1	1	1
ACCESS	RW	RW	RW	RW	RW	RW	RW	RW

**UV\_T7:0 (Bits 7–0):** Middle 8 bits of the direct ADC mapping of the desired UV protection threshold, with upper 2 MSB set to 01 and lower 4 LSB set to 0000. In other words, the equivalent UV threshold is mapped to:  $01\text{-UV\_T}<7:0>0000$ .

By default, UV\_TRIP is configured to a 0x97 setting.

Note that UV\_TRIP is based on the ADC voltage, which requires back-calculation using the GAIN and OFFSET values stored in AD CGAIN<4:0> and ADC OFFSET<7:0>.

**Table 7-14. CC\_CFG REGISTER (0x0B)**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	CC_CFG5	CC_CFG4	CC_CFG3	CC_CFG2	CC_CFG1	CC_CFG0
RESET	0	0	0	0	0	0	0	0
ACCESS	R	R	RW	RW	RW	RW	RW	RW

**CC\_CFG5:0 (Bits 5–0):** For optimal performance, these bits should be programmed to 0x19 upon device startup.

## 7.5.2 Read-Only Registers

**Table 7-15. ALL REGISTERS**

VC1_HI, _LO (0x0C–0x0D), VC2_HI, _LO (0x0E–0x0F), VC3_HI, _LO (0x10–0x11), VC4_HI, _LO (0x12–0x13), VC5_HI, _LO (0x14–0x15) / bq76930, bq76940: VC6_HI, _LO (0x16–0x17), VC7_HI, _LO (0x18–0x19), VC8_HI, _LO (0x1A–0x1B), VC9_HI, _LO (0x1C–0x1D), VC10_HI, _LO (0x1E–0x1F) / bq76940: VC11_HI, _LO (0x20–0x21), VC12_HI, _LO (0x22–0x23), VC13_HI, _LO (0x24–0x25), VC14_HI, _LO (0x26–0x27), VC15_HI, _LO (0x28–0x29)								
BIT	7	6	5	4	3	2	1	0
NAME	—	—	D13	D12	D11	D10	D9	D8
RESET	0	0	0	0	0	0	0	0
NAME	D7	D6	D5	D4	D3	D2	D1	D0
RESET	0	0	0	0	0	0	0	0

**D11:8 (Bits 3–0):** Cell “x” ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

**D7:0 (Bits 7–0):** Cell “x” ADC reading, lower 8 LSB.

**Table 7-16. BAT\_HI (0x2A) and BAT\_LO (0x2B)**

BIT	7	6	5	4	3	2	1	0
NAME	D15	D14	D13	D12	D11	D10	D9	D8
RESET	0	0	0	0	0	0	0	0
NAME	D7	D6	D5	D4	D3	D2	D1	D0
RESET	0	0	0	0	0	0	0	0

**D15:8 (Bits 7–0):**

BAT calculation based on adding up Cells 1–15, upper 8 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

**D7:0 (Bits 7–0):**

BAT calculation based on adding up Cells 1–15, lower 8 LSB

**Table 7-17. TS1\_HI (0x2C) and TS1\_LO (0x2D)**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	D13	D12	D11	D10	D9	D8
RESET	0	0	0	0	0	0	0	0
NAME	D7	D6	D5	D4	D3	D2	D1	D0
RESET	0	0	0	0	0	0	0	0

**D11:8 (Bits 3–0):** TS1 or DIETEMP ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

**D7:0 (Bits 7–0):** TS1 or DIETEMP ADC reading, lower 8 LSB

**Table 7-18. TS2\_HI (0x2E) and TS2\_LO (0x2F)**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	D13	D12	D11	D10	D9	D8

**Table 7-18. TS2\_HI (0x2E) and TS2\_LO (0x2F) (continued)**

BIT	7	6	5	4	3	2	1	0
RESET	0	0	0	0	0	0	0	0
NAME	D7	D6	D5	D4	D3	D2	D1	D0
RESET	0	0	0	0	0	0	0	0

**D11:8 (Bits 3–0):** TS2 ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

**D7:0 (Bits 7–0):** TS2 ADC reading, lower 8 LSB

**Table 7-19. TS3\_HI (0x30) and TS3\_LO (0x31)**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	D13	D12	D11	D10	D9	D8
RESET	0	0	0	0	0	0	0	0
NAME	D7	D6	D5	D4	D3	D2	D1	D0
RESET	0	0	0	0	0	0	0	0

**D11:8 (Bits 3–0):** TS3 ADC reading, upper 6 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

**D7:0 (Bits 7–0):** TS3 ADC reading, lower 8 LSB

**Table 7-20. CC\_HI (0x32) and CC\_LO (0x33)**

BIT	7	6	5	4	3	2	1	0
NAME	CC15	CC14	CC13	CC12	CC11	CC10	CC9	CC8
RESET	0	0	0	0	0	0	0	0
NAME	CC7	CC6	CC5	CC4	CC3	CC2	CC1	CC0
RESET	0	0	0	0	0	0	0	0

**CC15:8 (Bits 7–0):** Coulomb counter upper 8 MSB. Always returned as an atomic value if both high and low registers are read in the same transaction (using address auto-increment).

**CC7:0 (Bits 7–0):** Coulomb counter lower 8 LSB

**Table 7-21. ADCGAIN1 (0x50)**

BIT	7	6	5	4	3	2	1	0
NAME	—	—	—	—	ADCGAIN4	ADCGAIN3	—	—
RESET	—	—	—	—	—	—	—	—
ACCESS	R	R	R	R	R	R	R	R

**Table 7-22. ADCGAIN2 (0x59)**

BIT	7	6	5	4	3	2	1	0
NAME	ADCGAIN2	ADCGAIN1	ADCGAIN0	—	—	—	—	—
RESET	—	—	—	—	—	—	—	—
ACCESS	R	R	R	R	R	R	R	R

**ADCGAIN4:3 (Bits 3–2, address 0x50):**

ADC offset upper 2 MSB

**ADCGAIN2:0 (Bits 7–5, address 0x59):**

ADC offset lower 3 LSB

ADCGAIN<4:0> is a production-trimmed value for the ADC transfer function, in units of  $\mu\text{V}/\text{LSB}$ . The range is  $365 \mu\text{V}/\text{LSB}$  to  $396 \mu\text{V}/\text{LSB}$ , in steps of  $1 \mu\text{V}/\text{LSB}$ , and may be calculated as follows:

$$\text{GAIN} = 365 \mu\text{V}/\text{LSB} + (\text{ADCGAIN}<4:0>\text{in decimal}) \times (1 \mu\text{V}/\text{LSB})$$

Alternately, a conversion table is provided below:

ADC GAIN	Gain ( $\mu\text{V}/\text{LSB}$ )	ADC GAIN	Gain ( $\mu\text{V}/\text{LSB}$ )
0x00	365	0x10	381
0x01	366	0x11	382
0x02	367	0x12	383
0x03	368	0x13	384
0x04	369	0x14	385
0x05	370	0x15	386
0x06	371	0x16	387
0x07	372	0x17	388
0x08	373	0x18	389
0x09	374	0x19	390
0x0A	375	0x1A	391
0x0B	376	0x1B	392
0x0C	377	0x1C	393
0x0D	378	0x1D	394
0x0E	379	0x1E	395
0x0F	380	0x1F	396

**Table 7-23. ADCOFFSET (0x51)**

BIT	7	6	5	4	3	2	1	0
NAME	ADC OFFSET7	ADC OFFSET6	ADC OFFSET5	ADC OFFSET4	ADC OFFSET3	ADC OFFSET2	ADC OFFSET1	ADC OFFSET0
RESET	—	—	—	—	—	—	—	—
ACCESS	R	R	R	R	R	R	R	R

**ADCOFFSET7:0 (Bits 7–0):**

ADC offset, stored in 2's complement format in mV units. Positive full-scale range corresponds to 0x7F and negative full-scale corresponds to 0x80. The full-scale input range is  $-128 \text{ mV}$  to  $127 \text{ mV}$ , with an LSB of  $1 \text{ mV}$ .

Some example offsets are shown in the table below.

ADCOFFSET	Offset (mV)
0x00	0
0x01	1
0x7F	127
0x80	-128

ADCOFFSET	Offset (mV)
0x81	-127
0xFF	-1

## 8 Application and Implementation

### 8.1 Application Information

#### 8.1.1 Configuring Alternative Cell Counts

Each bq769x0 IC supports a variety of cell counts. The following tables provide guidance on which input pins to use, depending on the number of cells in the pack.

**Table 8-1. Cell Connections for bq76920**

Cell Input	3 Cells	4 Cells	5 Cells
VC5–VC4	CELL 3	CELL 4	CELL 5
VC4–VC3	short	short	CELL 4
VC3–VC2	short	CELL 3	CELL 3
VC2–VC1	CELL 2	CELL 2	CELL 2
VC1–VC0	CELL 1	CELL 1	CELL 1

**Table 8-2. Cell Connections for bq76930**

Cell Input	6 Cells	7 Cells	8 Cells	9 Cells	10 Cells
VC10–VC9	CELL 6	CELL 7	CELL 8	CELL 9	CELL 10
VC9–VC8	short	short	short	short	CELL 9
VC8–VC7	short	short	CELL 7	CELL 8	CELL 8
VC7–VC6	CELL 5	CELL 6	CELL 6	CELL 7	CELL 7
VC6–VC5b	CELL 4	CELL 5	CELL 5	CELL 6	CELL 6
VC5–VC4	CELL 3	CELL 4	CELL 4	CELL 5	CELL 5
VC4–VC3	short	short	short	CELL 4	CELL 4
VC3–VC2	short	CELL 3	CELL 3	CELL 3	CELL 3
VC2–VC1	CELL 2	CELL 2	CELL 2	CELL 2	CELL 2
VC1–VC0	CELL 1	CELL 1	CELL 1	CELL 1	CELL 1

**Table 8-3. Cell Connections for bq76940**

Cell Input	9 Cells	10 Cells	11 Cells	12 Cells	13 Cells	14 Cells	15 Cells
VC15–VC14	CELL 9	CELL 10	CELL 11	CELL 12	CELL 13	CELL 14	CELL 15
VC14–VC13	short	short	short	short	short	short	CELL 14
VC13–VC12	short	short	short	CELL 11	CELL 12	CELL 13	CELL 13
VC12–VC11	CELL 8	CELL 9	CELL 10	CELL 10	CELL 11	CELL 12	CELL 12
VC11–VC10b	CELL 7	CELL 8	CELL 9	CELL 9	CELL 10	CELL 11	CELL 11
VC10–VC9	CELL 6	CELL 7	CELL 8	CELL 8	CELL 9	CELL 10	CELL 10
VC9–VC8	short	short	short	short	short	CELL 9	CELL 9
VC8–VC7	short	short	CELL 7	CELL 7	CELL 8	CELL 8	CELL 8
VC7–VC6	CELL 5	CELL 6	CELL 6	CELL 6	CELL 7	CELL 7	CELL 7
VC6–VC5b	CELL 4	CELL 5	CELL 5	CELL 5	CELL 6	CELL 6	CELL 6
VC5–VC4	CELL 3	CELL 4	CELL 4	CELL 4	CELL 5	CELL 5	CELL 5
VC4–VC3	short	short	short	short	CELL 4	CELL 4	CELL 4
VC3–VC2	short	CELL 3	CELL 3	CELL 3	CELL 3	CELL 3	CELL 3
VC2–VC1	CELL 2	CELL 2	CELL 2	CELL 2	CELL 2	CELL 2	CELL 2
VC1–VC0	CELL 1	CELL 1	CELL 1	CELL 1	CELL 1	CELL 1	CELL 1



## 8.2 Typical Applications

### CAUTION

The external circuitry shown in the following schematics are a minimum requirement to ensure device robustness, during both cell connection to the PCB and normal operation. For more detailed guidance, please refer to the Reference Schematic (when available).

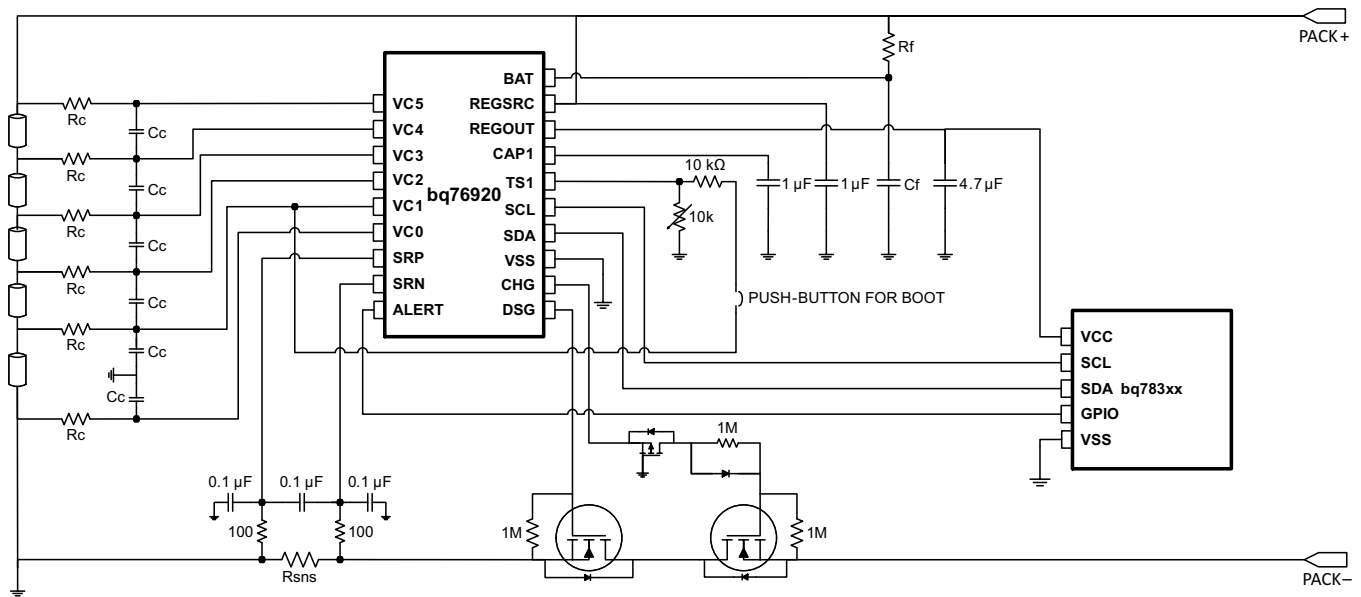
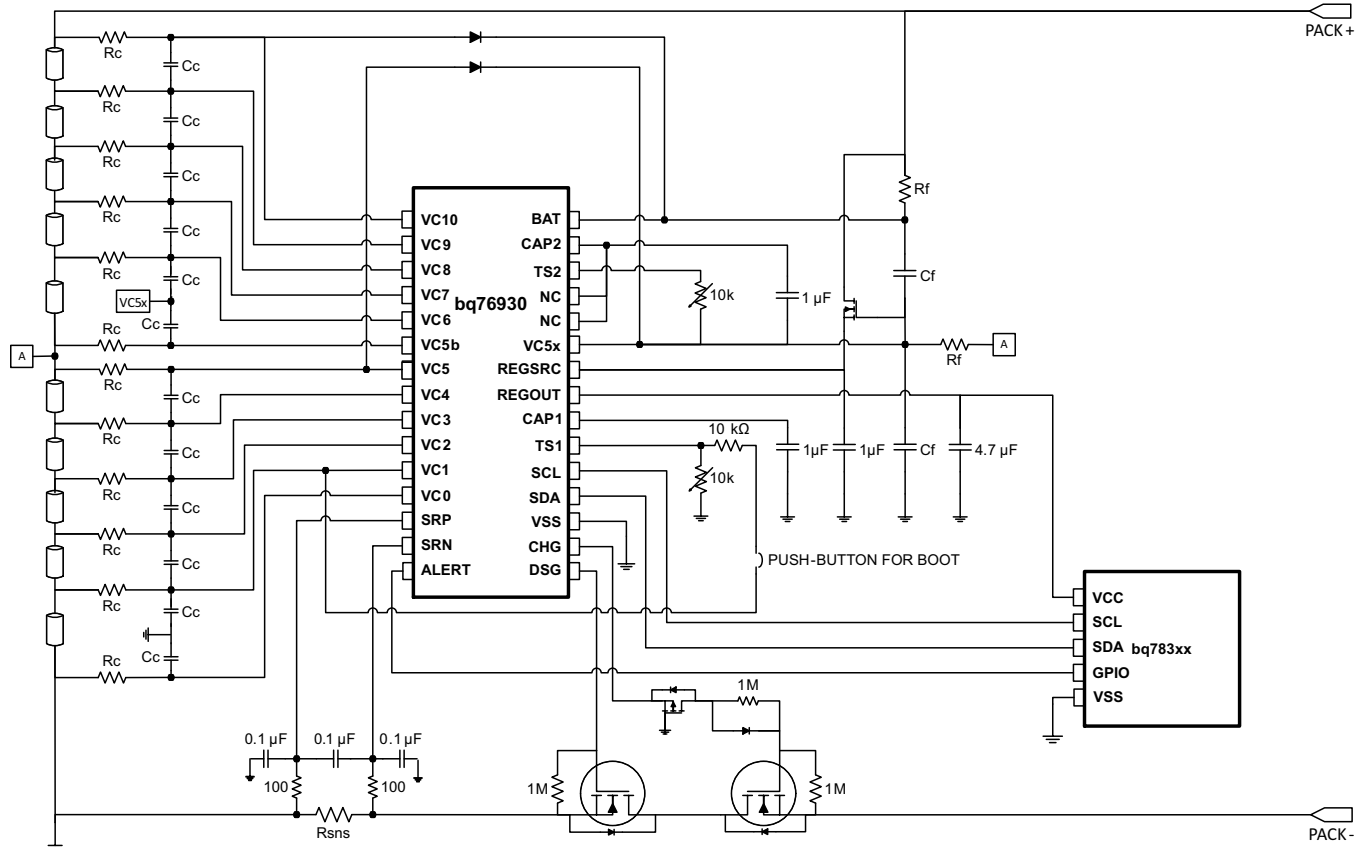


Figure 8-1. bq76920 with bq783xx Companion Controller IC

**bq76920, bq76930, bq76940**

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**Figure 8-2. bq76930 with bq783xx Companion Controller IC**

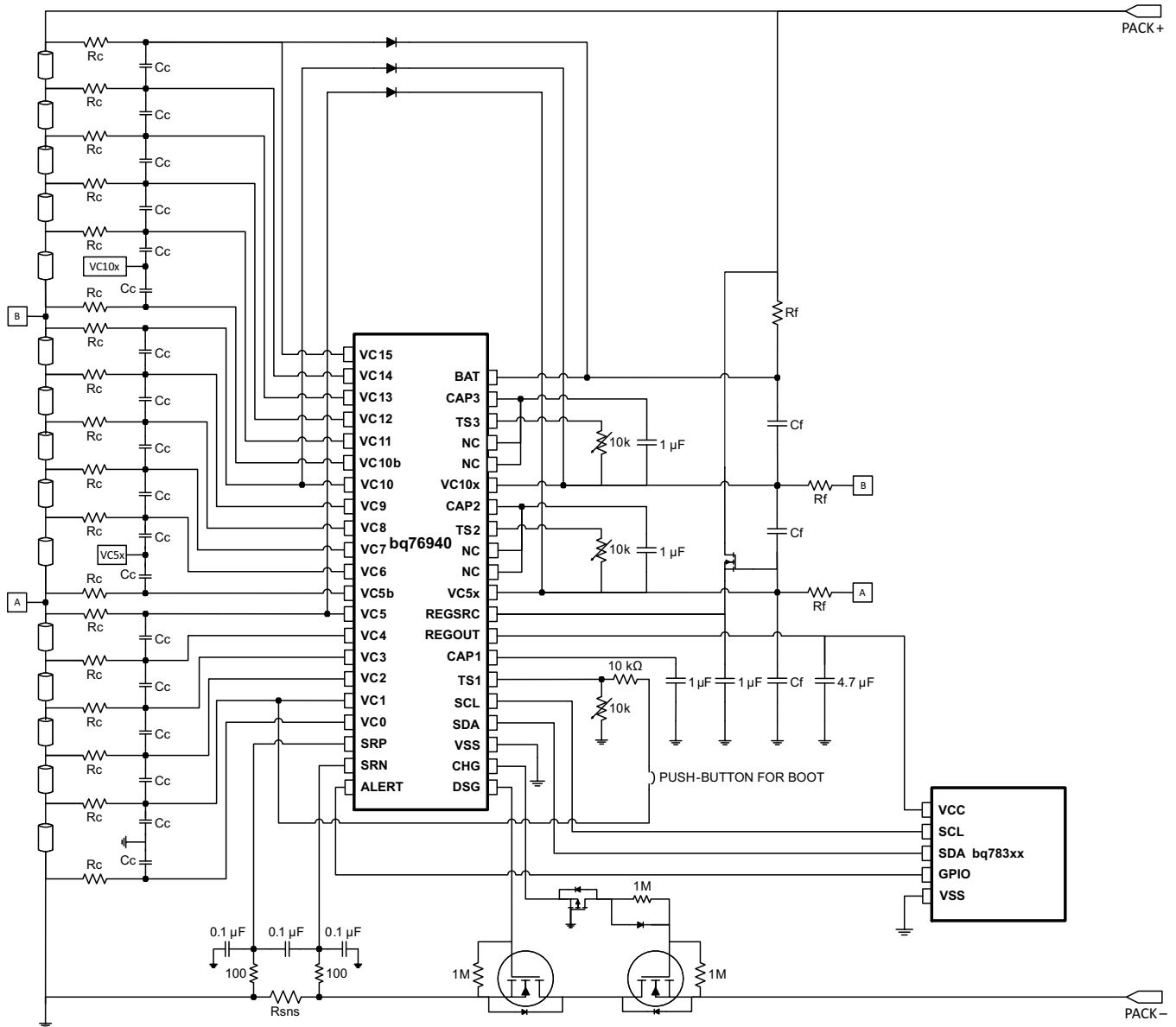


Figure 8-3. bq76940 with bq783xx Companion Controller IC

## 9 器件和文档支持

### 9.1 文档支持

#### 9.1.1 相关文档

要获得相关文档，请见下方的：《bq76920 评估模块用户指南》([SLVU924](#))。

## 9.2 相关链接

以下表格列出了快速访问链接。范围包括技术文档、支持与社区资源、工具和软件，以及样片或购买的快速访问。

**Table 9-1. 相关链接**

部件	产品文件夹	样片与购买	技术文档	工具与软件	支持与社区
bq76920	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>
bq76930	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>
bq76940	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>	<a href="#">请单击此处</a>

## 9.3 Trademarks

I<sup>2</sup>C is a trademark of NXP B.V. Corporation.

## 9.4 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

## 9.5 出口管制提示

接收方同意：如果美国或其他适用法律限制或禁止将通过本协议的披露方获得的任何产品或技术数据（其中包括软件）（见美国、欧盟和其他出口管理条例之定义）、或者其他适用国家条例限制的任何受管制产品或此项技术的任何直接产品出口或再出口至任何目的地，那么在没有事先获得美国商务部和其他相关政府机构授权的情况下，接收方不得在知情的情况下，以直接或间接的方式将其出口。

## 9.6 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms and definitions.

## 10 机械封装和可订购信息

以下页中包括机械封装和可订购信息。 这些信息是针对指定器件可提供的最新数据。 这些数据会在无通知且不对本文档进行修订的情况下发生改变。 欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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放大器和线性器件	<a href="http://www.ti.com.cn/amplifiers">www.ti.com.cn/amplifiers</a>	计算机及周边	<a href="http://www.ti.com.cn/computer">www.ti.com.cn/computer</a>
数据转换器	<a href="http://www.ti.com.cn/dataconverters">www.ti.com.cn/dataconverters</a>	消费电子	<a href="http://www.ti.com.cn/consumer-apps">www.ti.com.cn/consumer-apps</a>
DLP® 产品	<a href="http://www.dlp.com">www.dlp.com</a>	能源	<a href="http://www.ti.com.cn/energy">www.ti.com.cn/energy</a>
DSP - 数字信号处理器	<a href="http://www.ti.com.cn/dsp">www.ti.com.cn/dsp</a>	工业应用	<a href="http://www.ti.com.cn/industrial">www.ti.com.cn/industrial</a>
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接口	<a href="http://www.ti.com.cn/interface">www.ti.com.cn/interface</a>	安防应用	<a href="http://www.ti.com.cn/security">www.ti.com.cn/security</a>
逻辑	<a href="http://www.ti.com.cn/logic">www.ti.com.cn/logic</a>	汽车电子	<a href="http://www.ti.com.cn/automotive">www.ti.com.cn/automotive</a>
电源管理	<a href="http://www.ti.com.cn/power">www.ti.com.cn/power</a>	视频和影像	<a href="http://www.ti.com.cn/video">www.ti.com.cn/video</a>
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OMAP应用处理器	<a href="http://www.ti.com.cn/omap">www.ti.com.cn/omap</a>		
无线连通性	<a href="http://www.ti.com.cn/wirelessconnectivity">www.ti.com.cn/wirelessconnectivity</a>	德州仪器在线技术支持社区	<a href="http://www.deyisupport.com">www.deyisupport.com</a>

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**PACKAGING INFORMATION**

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
BQ7692000PW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7692000	<a href="#">Samples</a>
BQ7692000PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7692000	<a href="#">Samples</a>
BQ7692003PW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7692003	<a href="#">Samples</a>
BQ7692003PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7692003	<a href="#">Samples</a>
BQ7692006PW	ACTIVE	TSSOP	PW	20	70	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7692006	<a href="#">Samples</a>
BQ7692006PWR	ACTIVE	TSSOP	PW	20	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7692006	<a href="#">Samples</a>
BQ7693000DBT	ACTIVE	TSSOP	DBT	30	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693000	<a href="#">Samples</a>
BQ7693000DBTR	ACTIVE	TSSOP	DBT	30	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693000	<a href="#">Samples</a>
BQ7693001DBT	ACTIVE	TSSOP	DBT	30	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693001	<a href="#">Samples</a>
BQ7693001DBTR	ACTIVE	TSSOP	DBT	30	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693001	<a href="#">Samples</a>
BQ7693003DBT	ACTIVE	TSSOP	DBT	30	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693003	<a href="#">Samples</a>
BQ7693003DBTR	ACTIVE	TSSOP	DBT	30	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693003	<a href="#">Samples</a>
BQ7693006DBT	ACTIVE	TSSOP	DBT	30	60	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693006	<a href="#">Samples</a>
BQ7693006DBTR	ACTIVE	TSSOP	DBT	30	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7693006	<a href="#">Samples</a>
BQ7694000DBT	ACTIVE	TSSOP	DBT	44	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694000	<a href="#">Samples</a>
BQ7694000DBTR	ACTIVE	TSSOP	DBT	44	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694000	<a href="#">Samples</a>
BQ7694001DBT	ACTIVE	TSSOP	DBT	44	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694001	<a href="#">Samples</a>

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
BQ7694001DBTR	ACTIVE	TSSOP	DBT	44	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694001	<a href="#">Samples</a>
BQ7694002DBT	ACTIVE	TSSOP	DBT	44	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694002	<a href="#">Samples</a>
BQ7694002DBTR	ACTIVE	TSSOP	DBT	44	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694002	<a href="#">Samples</a>
BQ7694003DBT	ACTIVE	TSSOP	DBT	44	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694003	<a href="#">Samples</a>
BQ7694003DBTR	ACTIVE	TSSOP	DBT	44	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694003	<a href="#">Samples</a>
BQ7694006DBT	ACTIVE	TSSOP	DBT	44	40	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694006	<a href="#">Samples</a>
BQ7694006DBTR	ACTIVE	TSSOP	DBT	44	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	BQ7694006	<a href="#">Samples</a>

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

**LIFEBUY:** TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

**NRND:** Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSELETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

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**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

**Green (RoHS & no Sb/Br):** TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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**TAPE AND REEL INFORMATION**

**QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
BQ7692000PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
BQ7692003PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1
BQ7692006PWR	TSSOP	PW	20	2000	330.0	16.4	6.95	7.1	1.6	8.0	16.0	Q1

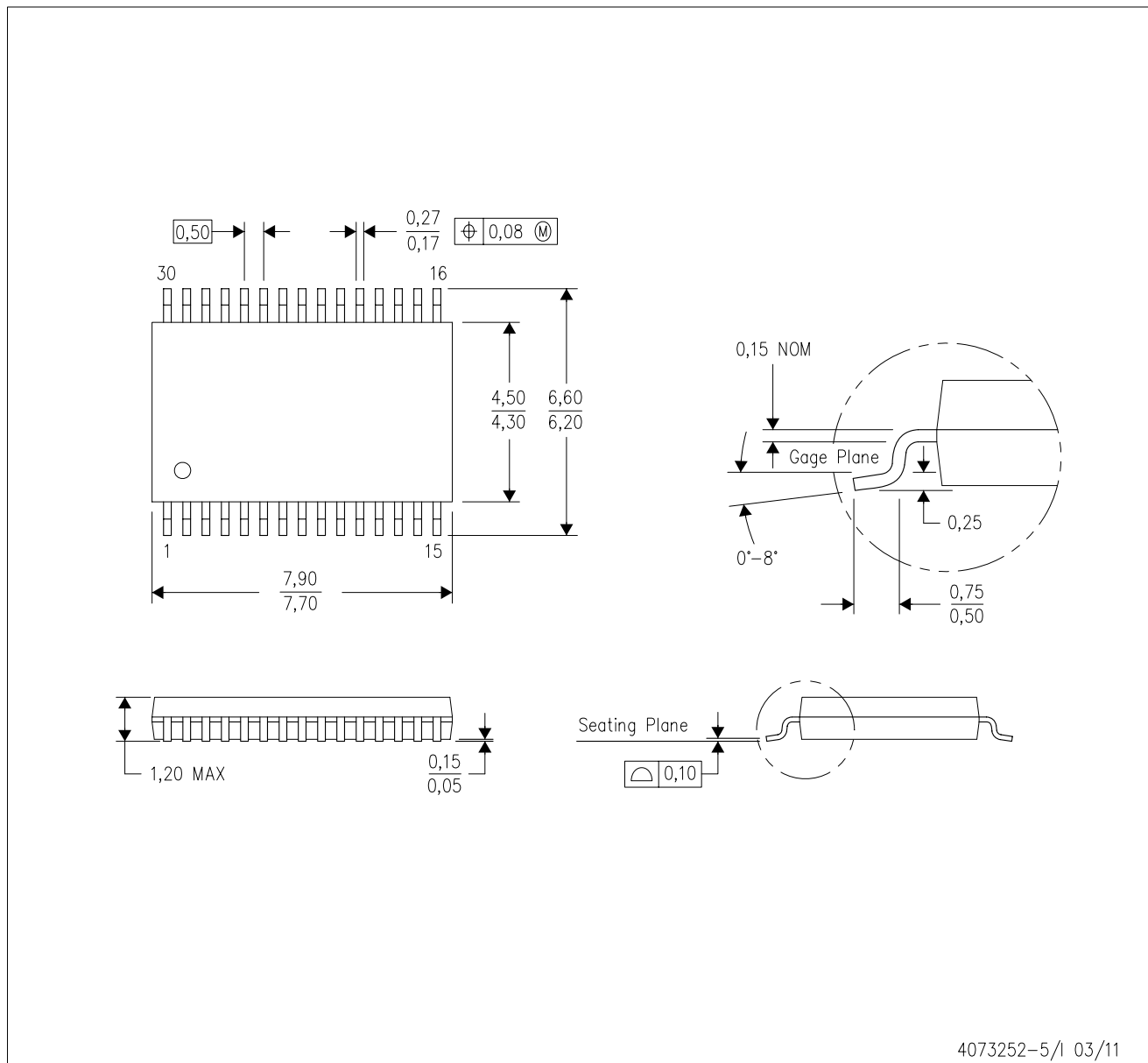
**TAPE AND REEL BOX DIMENSIONS**


\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
BQ7692000PWR	TSSOP	PW	20	2000	367.0	367.0	38.0
BQ7692003PWR	TSSOP	PW	20	2000	367.0	367.0	38.0
BQ7692006PWR	TSSOP	PW	20	2000	367.0	367.0	38.0

DBT (R-PDSO-G30)

PLASTIC SMALL OUTLINE

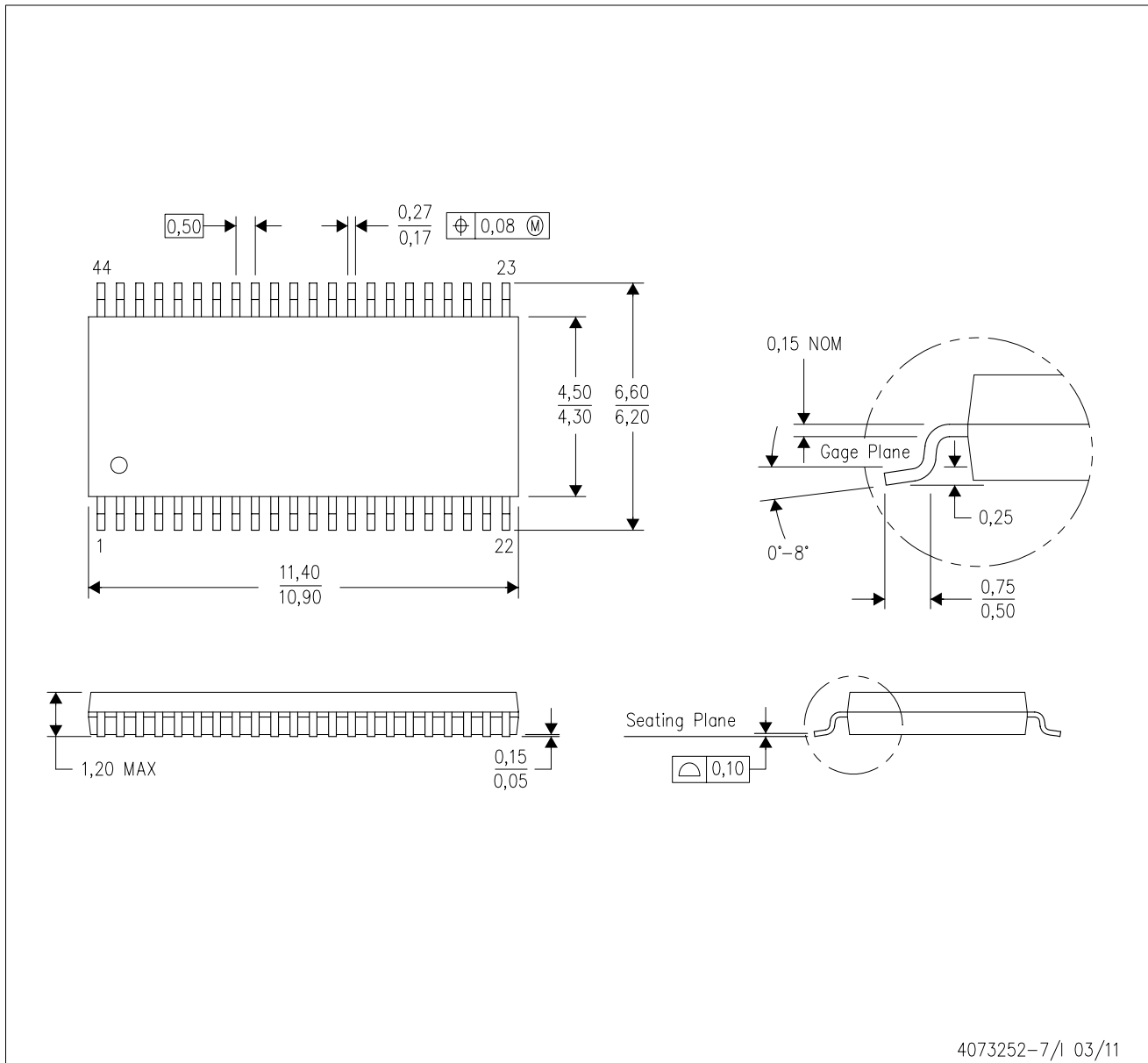


- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion.
  - D. Falls within JEDEC MO-153.

# MECHANICAL DATA

DBT (R-PDSO-G44)

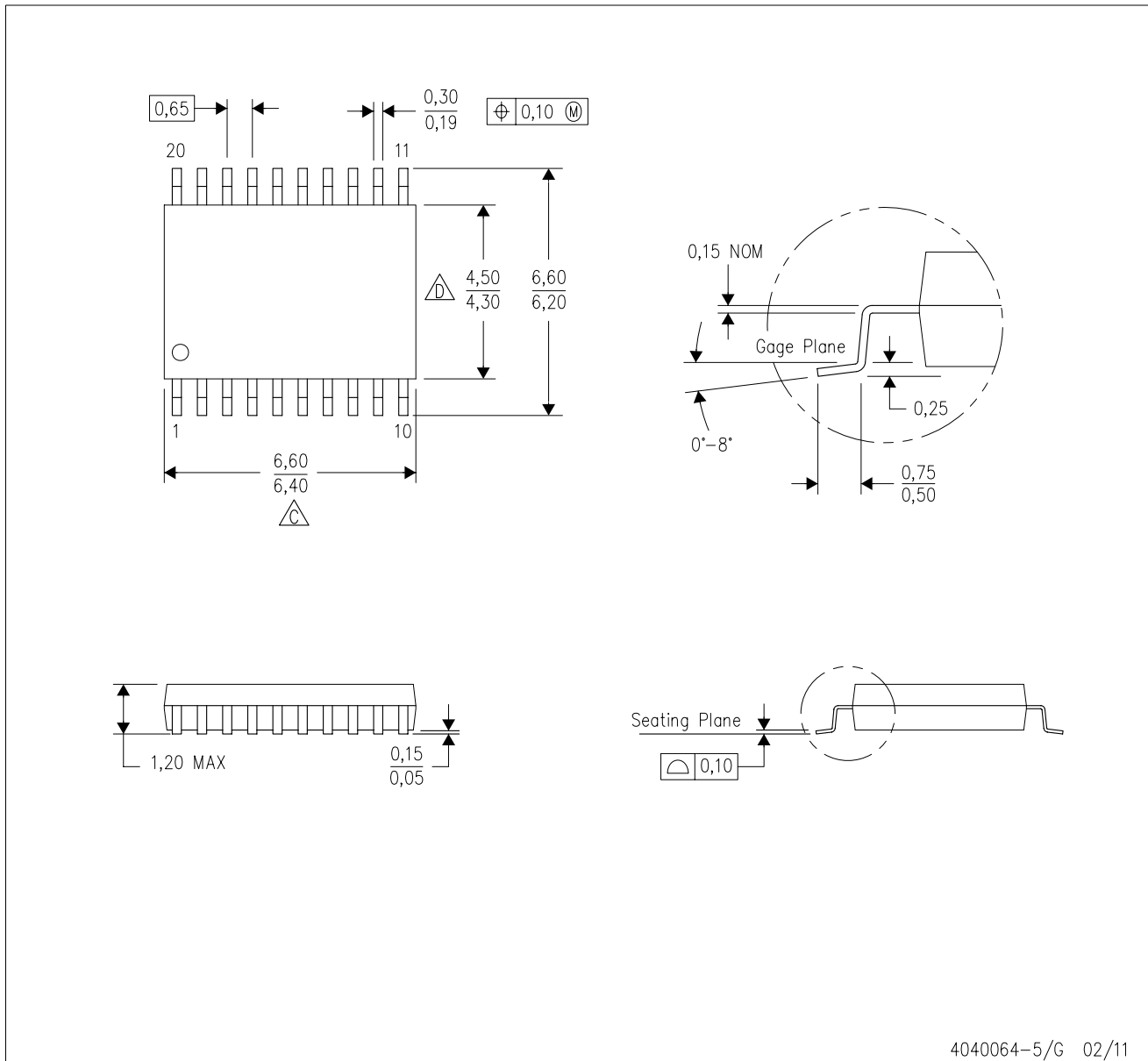
PLASTIC SMALL OUTLINE





- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  - C. Body dimensions do not include mold flash or protrusion.

PW (R-PDSO-G20)

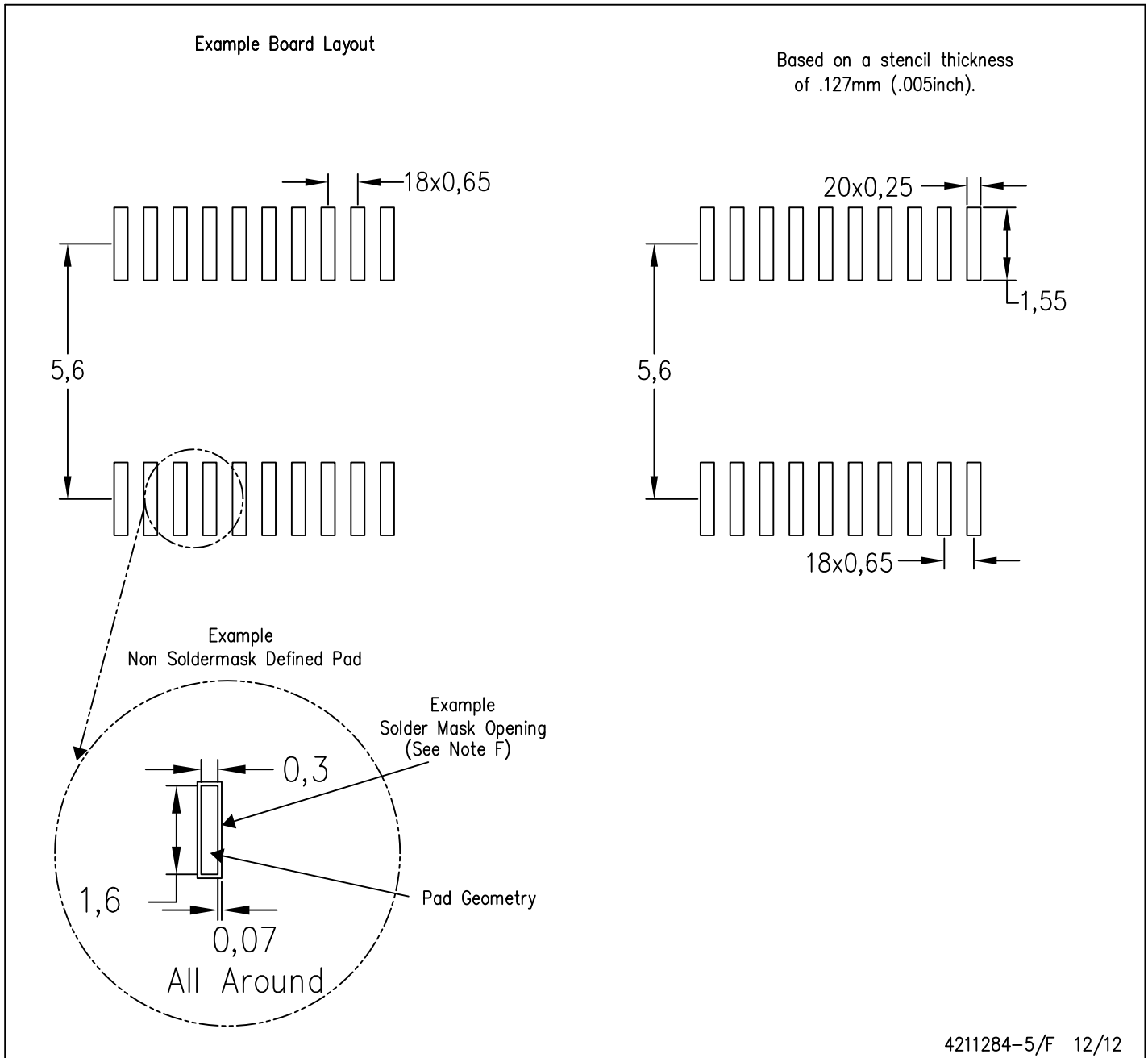
PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M-1994.
  - B. This drawing is subject to change without notice.
  -  Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
  -  Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
  - E. Falls within JEDEC MO-153

PW (R-PDSO-G20)

PLASTIC SMALL OUTLINE



- NOTES:
- A. All linear dimensions are in millimeters.
  - B. This drawing is subject to change without notice.
  - C. Publication IPC-7351 is recommended for alternate design.
  - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
  - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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TI 已明确指定符合 ISO/TS16949 要求的产品, 这些产品主要用于汽车。在任何情况下, 因使用非指定产品而无法达到 ISO/TS16949 要求, TI 不承担任何责任。

产品	应用
数字音频	<a href="http://www.ti.com.cn/audio">www.ti.com.cn/audio</a> 通信与电信 <a href="http://www.ti.com.cn/telecom">www.ti.com.cn/telecom</a>
放大器和线性器件	<a href="http://www.ti.com.cn/amplifiers">www.ti.com.cn/amplifiers</a> 计算机及周边 <a href="http://www.ti.com.cn/computer">www.ti.com.cn/computer</a>
数据转换器	<a href="http://www.ti.com.cn/dataconverters">www.ti.com.cn/dataconverters</a> 消费电子 <a href="http://www.ti.com.cn/consumer-apps">www.ti.com.cn/consumer-apps</a>
DLP® 产品	<a href="http://www.dlp.com">www.dlp.com</a> 能源 <a href="http://www.ti.com.cn/energy">www.ti.com.cn/energy</a>
DSP - 数字信号处理器	<a href="http://www.ti.com.cn/dsp">www.ti.com.cn/dsp</a> 工业应用 <a href="http://www.ti.com.cn/industrial">www.ti.com.cn/industrial</a>
时钟和计时器	<a href="http://www.ti.com.cn/clockandtimers">www.ti.com.cn/clockandtimers</a> 医疗电子 <a href="http://www.ti.com.cn/medical">www.ti.com.cn/medical</a>
接口	<a href="http://www.ti.com.cn/interface">www.ti.com.cn/interface</a> 安防应用 <a href="http://www.ti.com.cn/security">www.ti.com.cn/security</a>
逻辑	<a href="http://www.ti.com.cn/logic">www.ti.com.cn/logic</a> 汽车电子 <a href="http://www.ti.com.cn/automotive">www.ti.com.cn/automotive</a>
电源管理	<a href="http://www.ti.com.cn/power">www.ti.com.cn/power</a> 视频和影像 <a href="http://www.ti.com.cn/video">www.ti.com.cn/video</a>
微控制器 (MCU)	<a href="http://www.ti.com.cn/microcontrollers">www.ti.com.cn/microcontrollers</a>
RFID 系统	<a href="http://www.ti.com.cn/rfidsys">www.ti.com.cn/rfidsys</a>
OMAP应用处理器	<a href="http://www.ti.com/omap">www.ti.com/omap</a>
无线连通性	<a href="http://www.ti.com.cn/wirelessconnectivity">www.ti.com.cn/wirelessconnectivity</a> 德州仪器在线技术支持社区 <a href="http://www.deyisupport.com">www.deyisupport.com</a>

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